

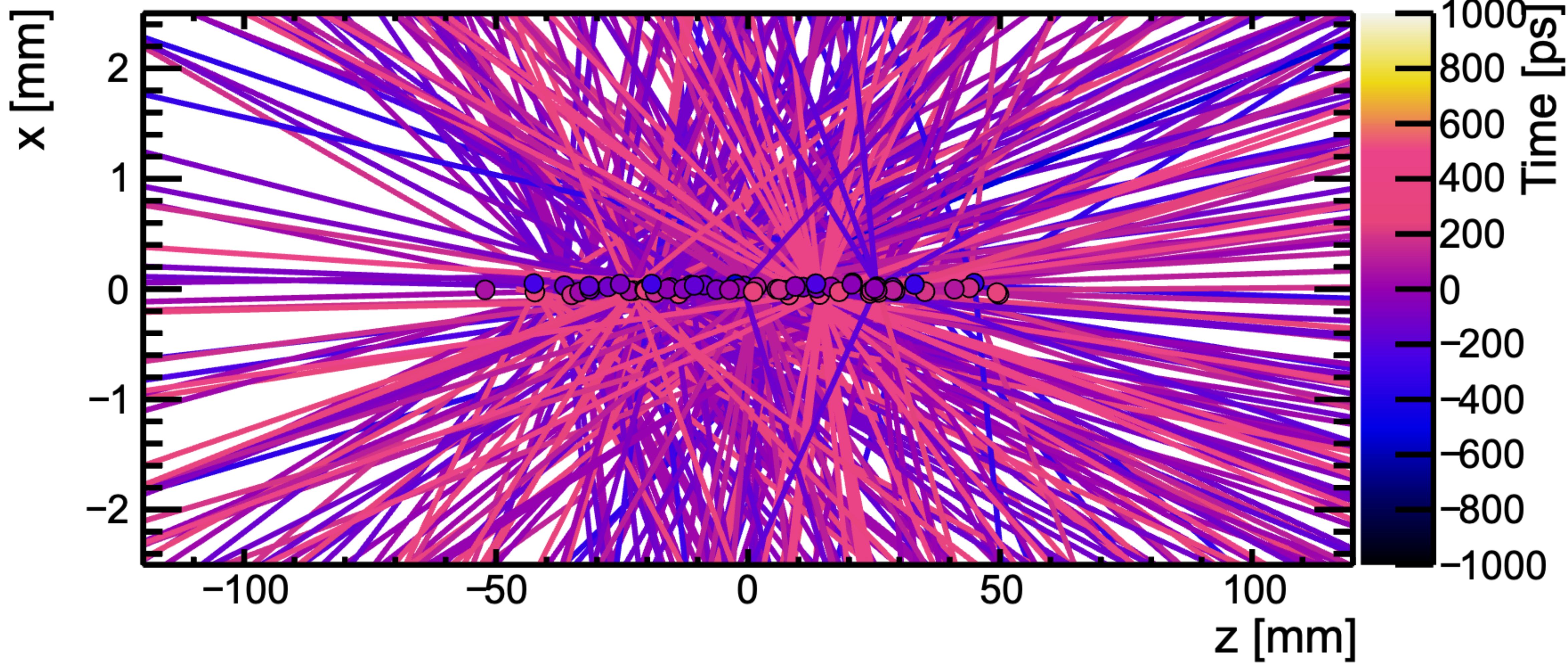
Development of the Next Generation Silicon Sensors for the LHCb experiment

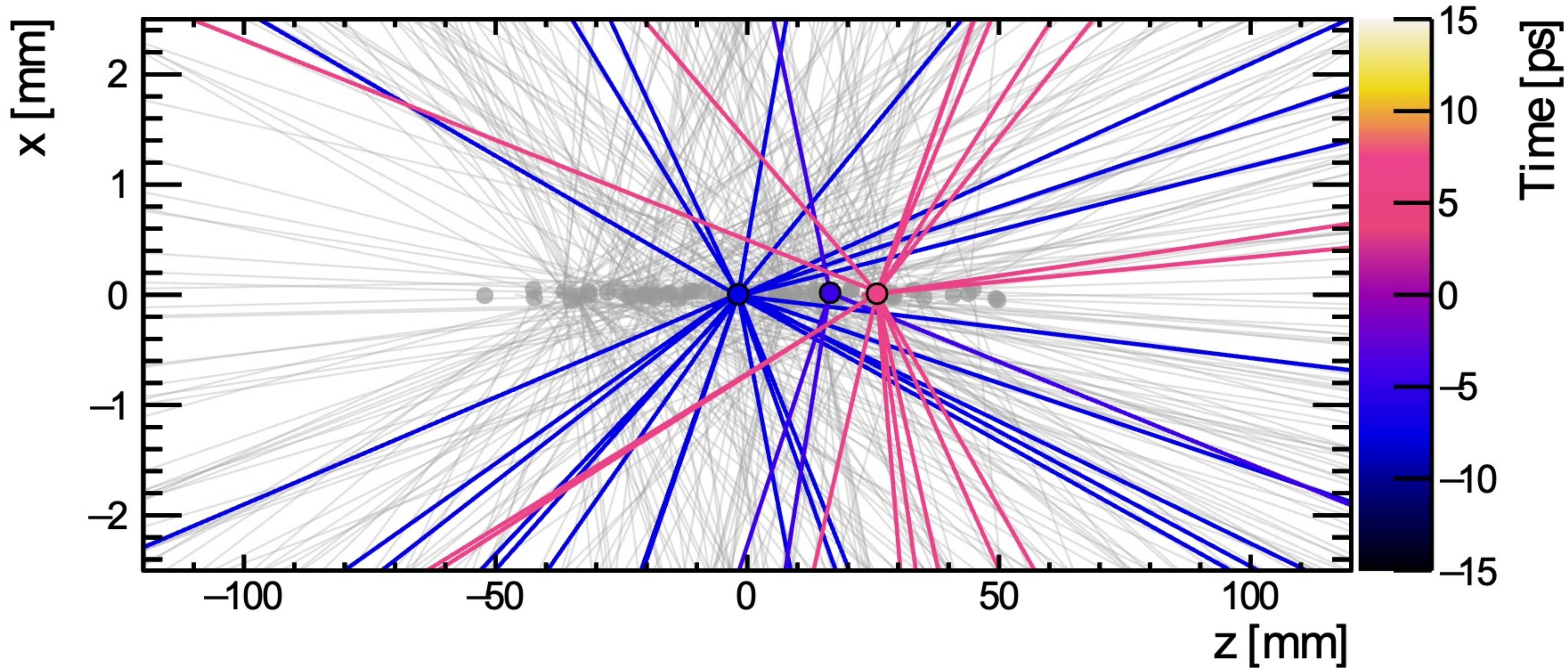
27-29.5. 2025 P4F colloquium

Peter Švihra

A high-magnification, grayscale microscopic image showing the intricate grid patterns of silicon microstrip detectors. The image has a strong blue tint.

Motivation:
Need for a precise track timing and
radiation hardness in HL-LHC
experiments

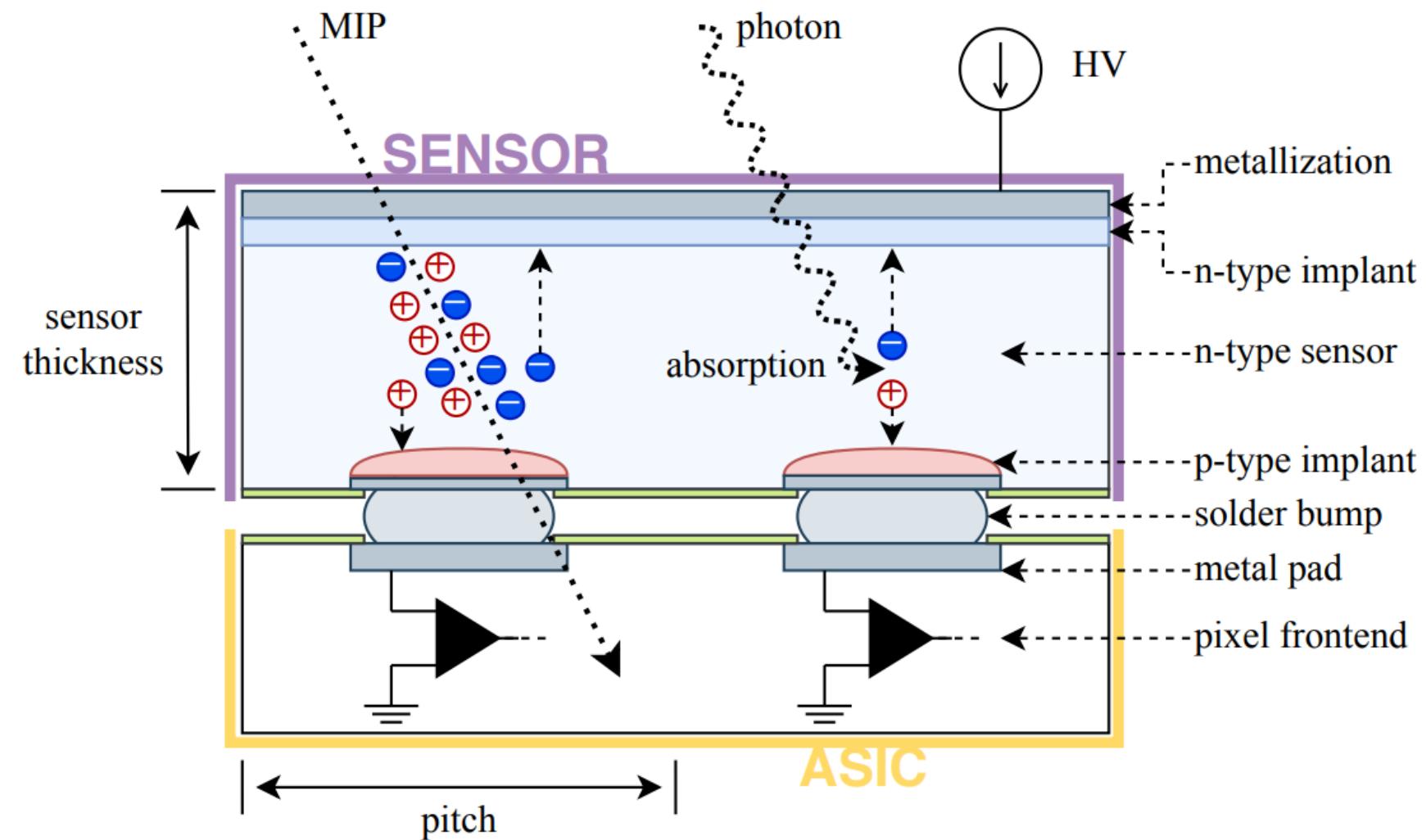




Semiconductor detectors – in a nutshell

Hybrid

- current predominant detector concept
- vertex detection & track-timing



Separate sensor & ASIC → intercon. hybrid detector

- sep. R&D and manufacturing process

✓ Efficiency, spatial and timing resolution

R&D

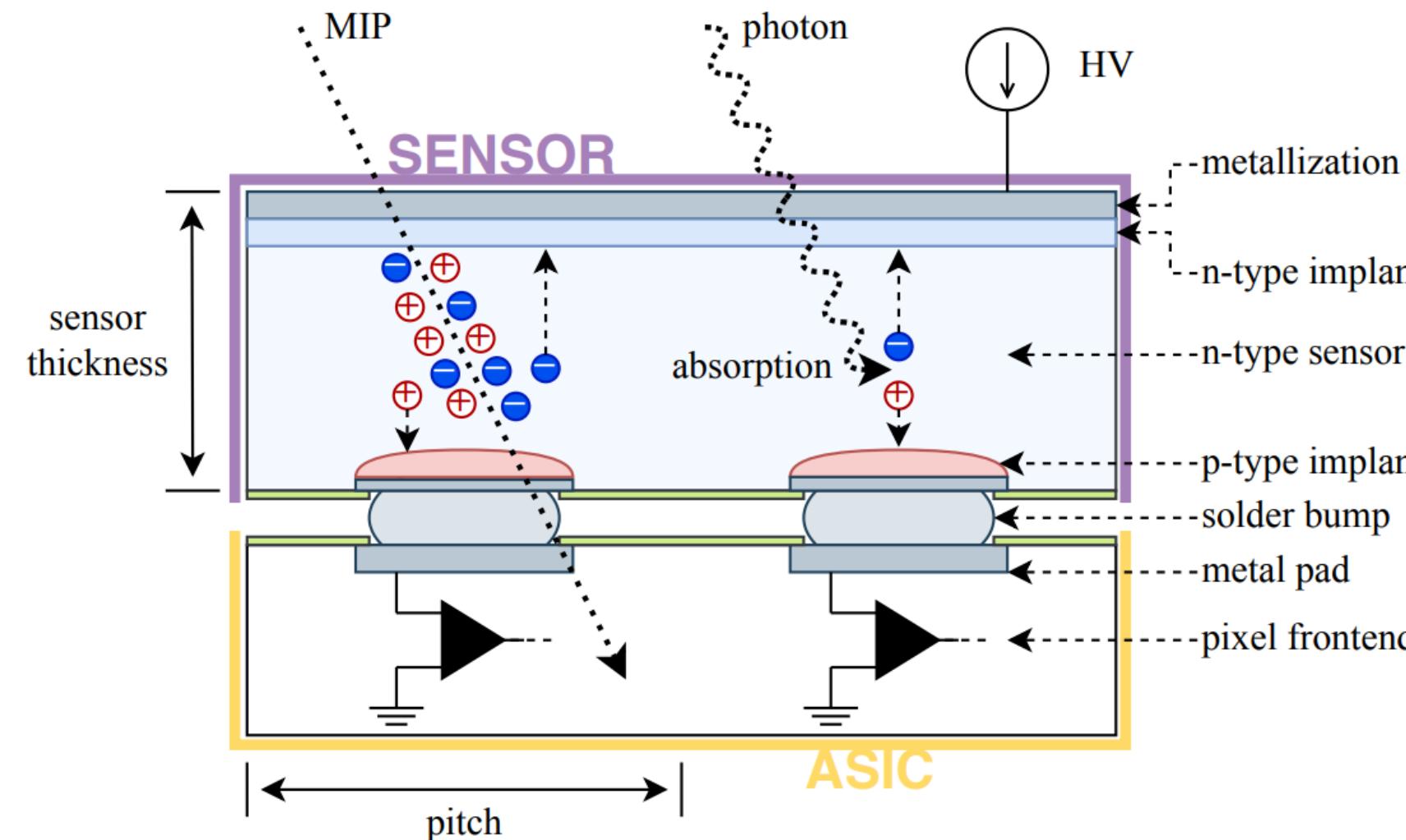
✗ Material budget

✗ Interconnection cost and minimum achievable pitch

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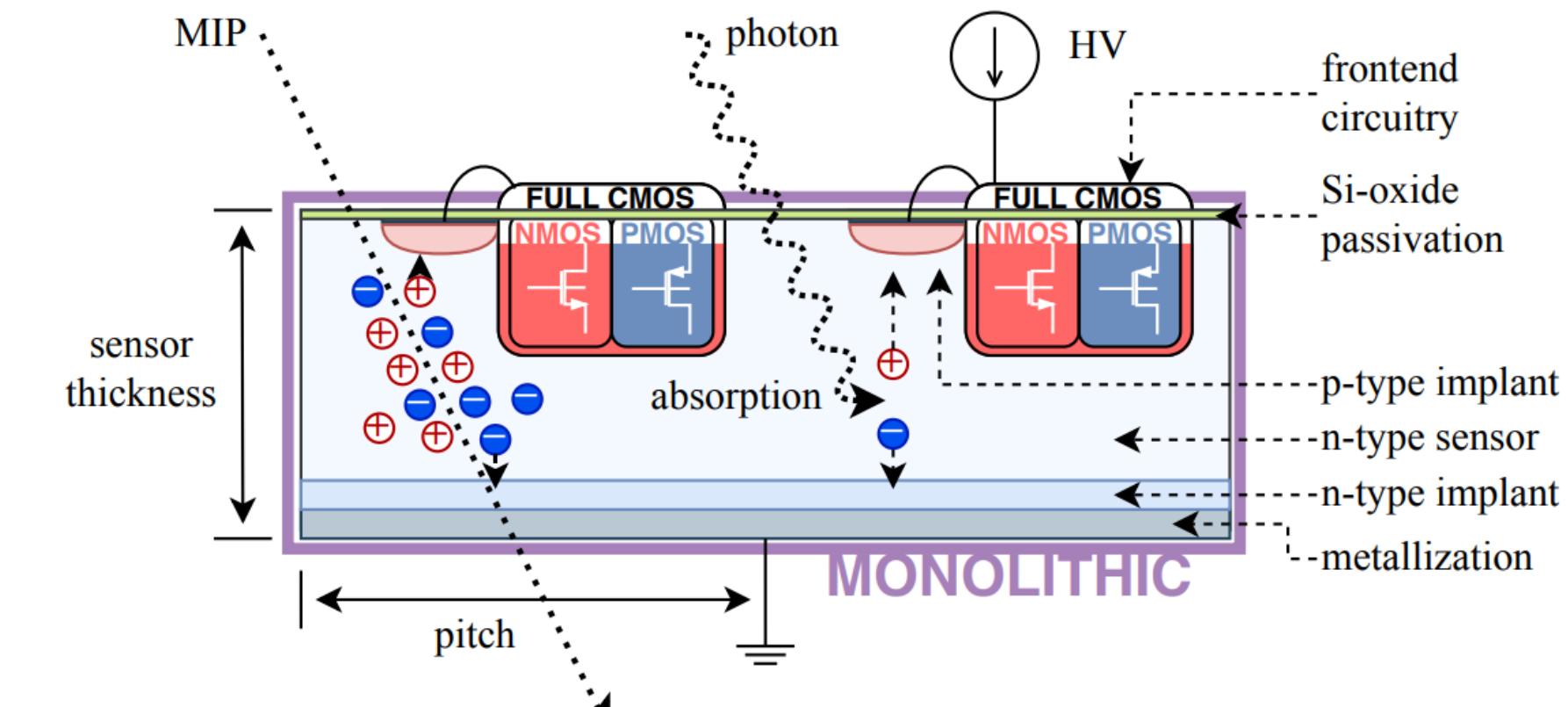
✗ Material budget

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R&D

Monolithic CMOS

- future detector concept
- vertex detector & tracker



Sensor and readout electronics fully integrated

- Adapted industrial manufacturing technologies

✓ Simplified, cost-effective construction

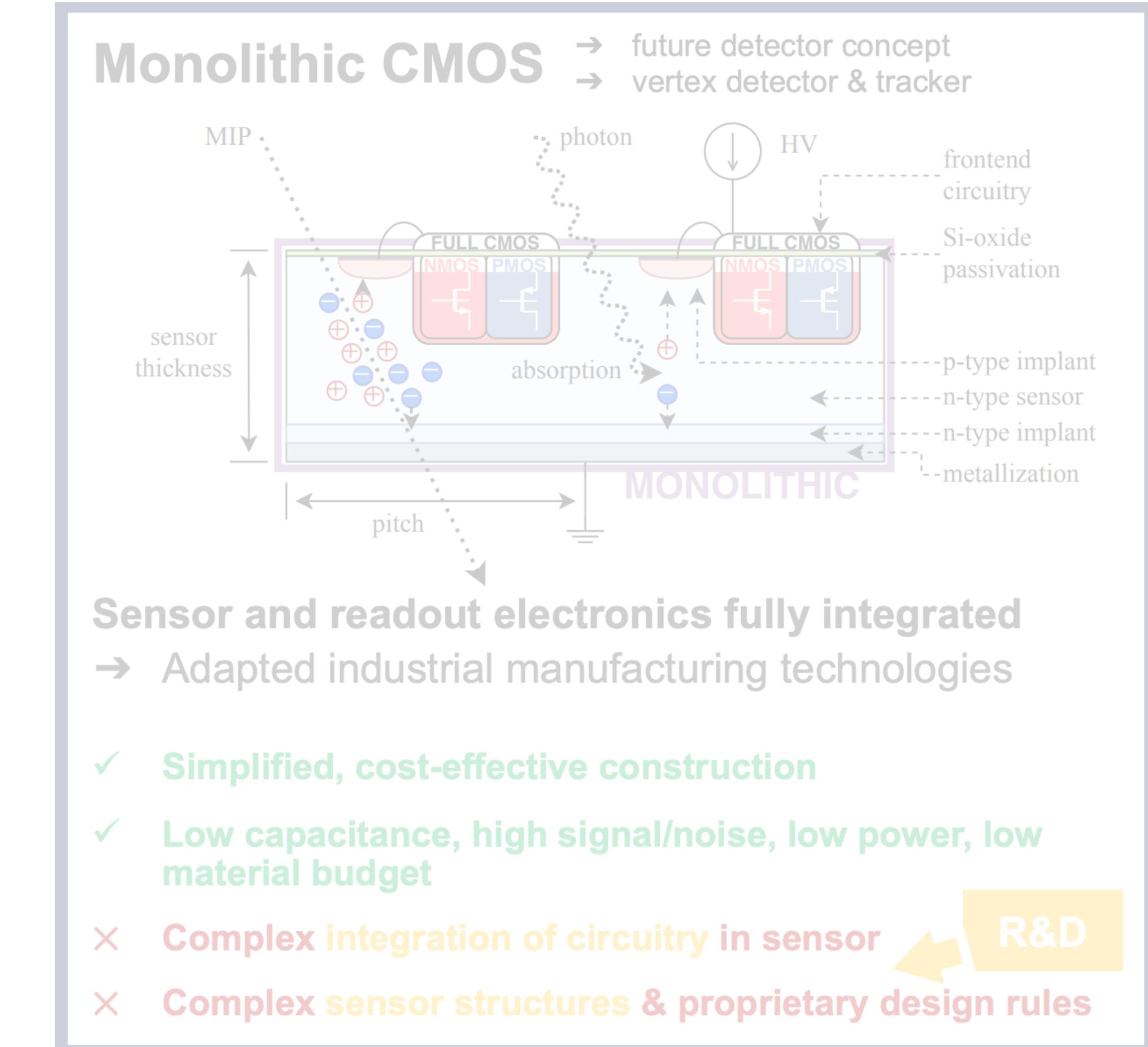
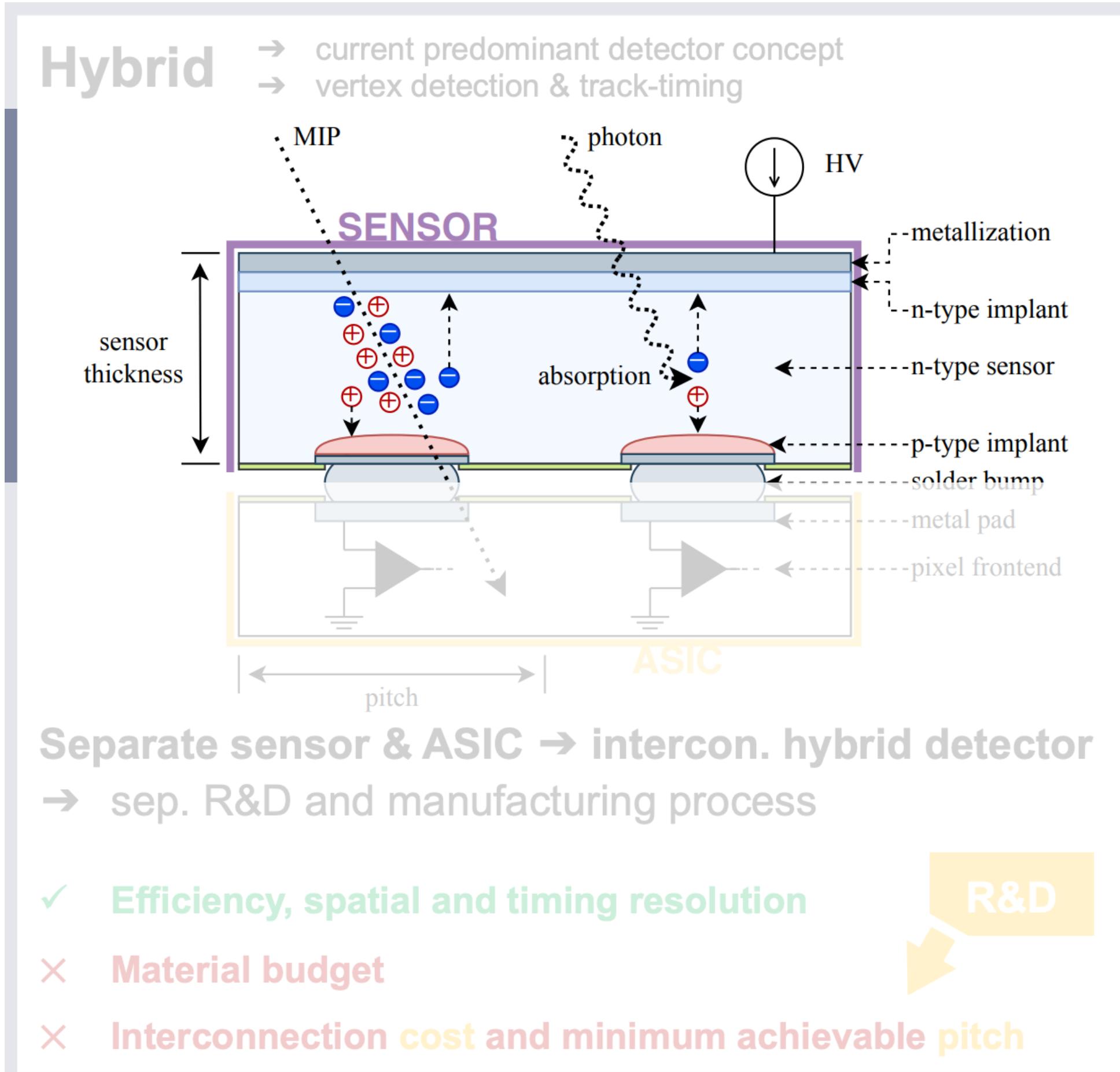
✓ Low capacitance, high signal/noise, low power, low material budget

✗ Complex integration of circuitry in sensor

R&D

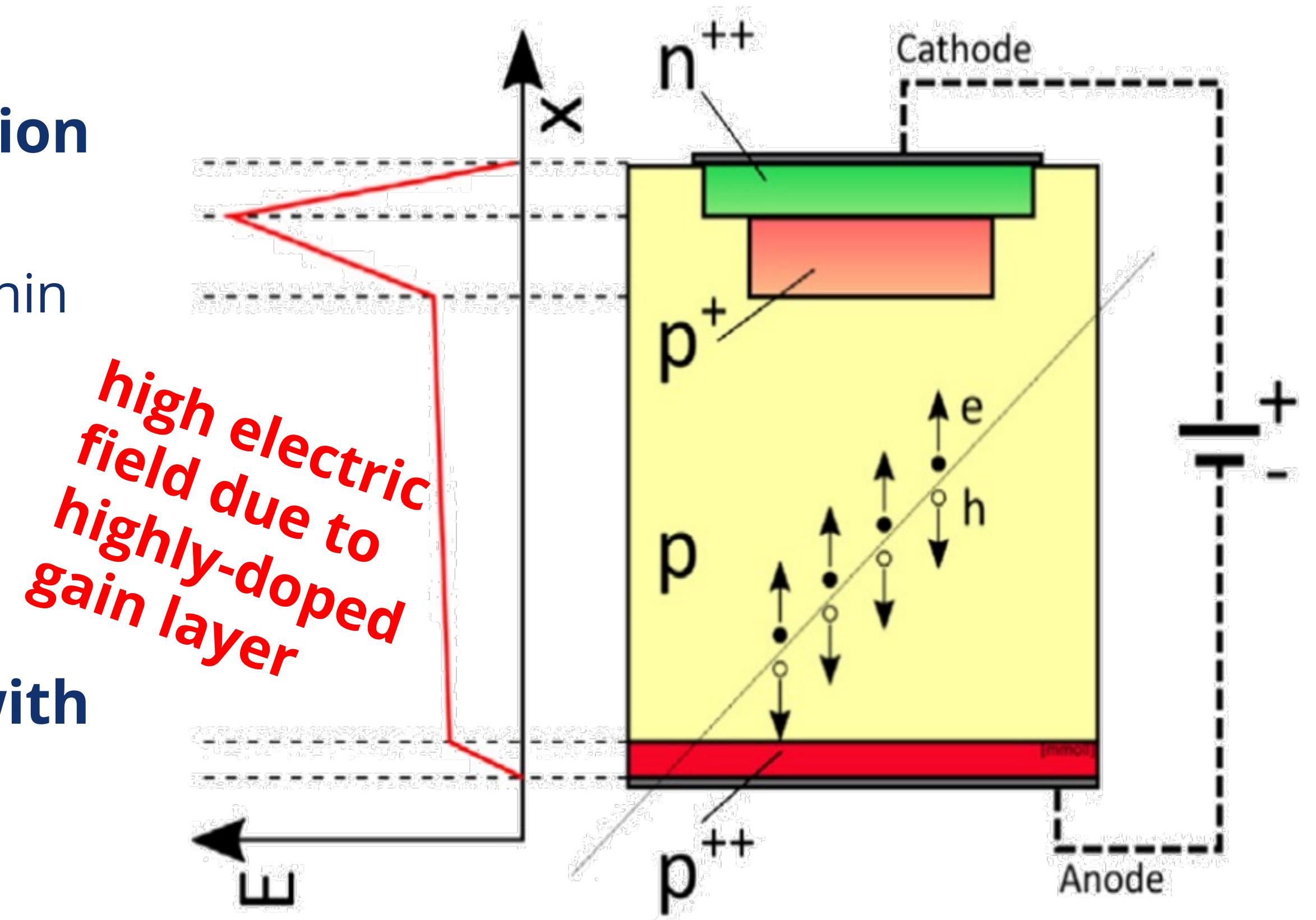
✗ Complex sensor structures & proprietary design rules

Semiconductor detectors – in a nutshell



Low Gain Avalanche Detectors (LGADs)

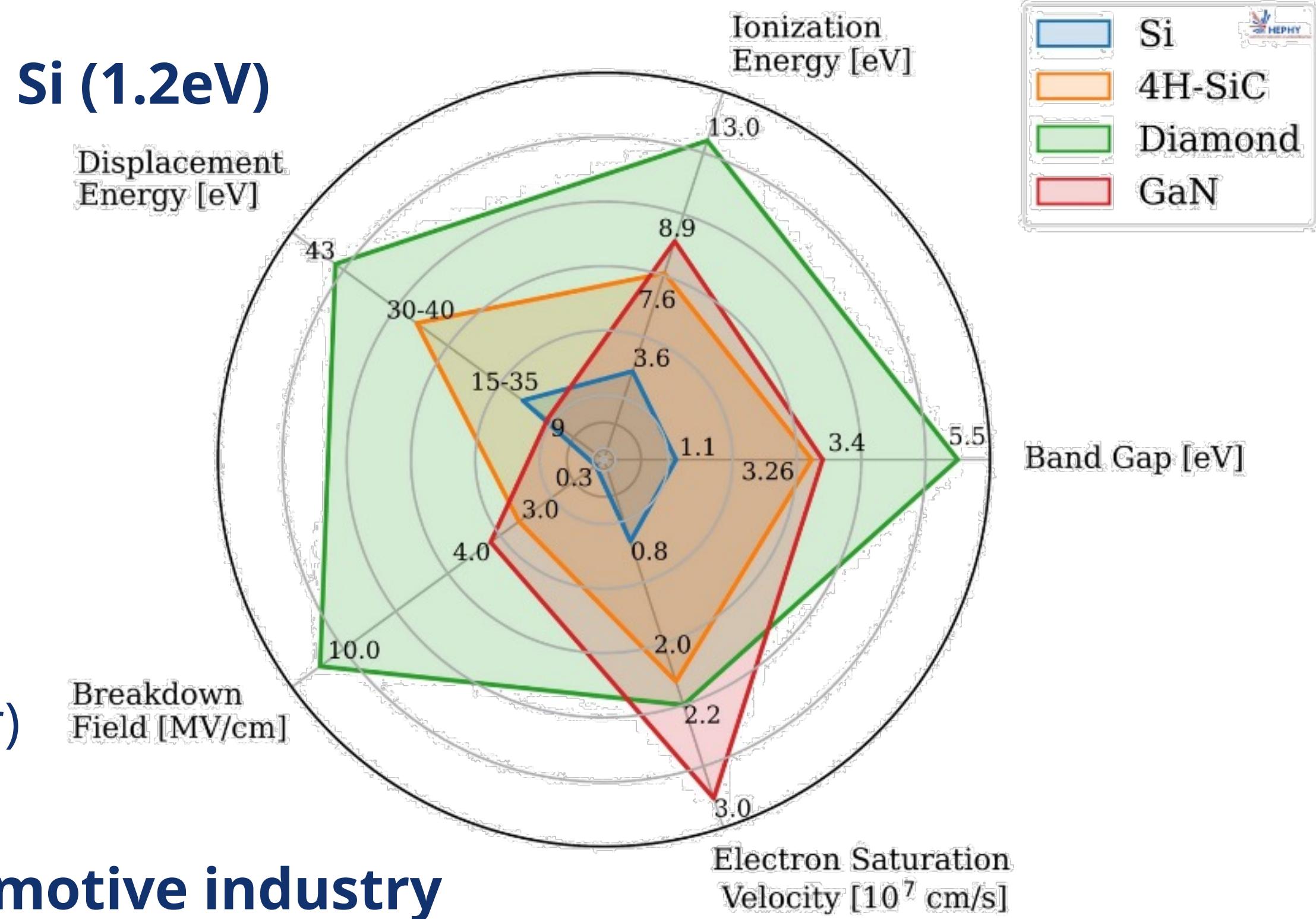
- Benefits of intrinsic charge multiplication
 - Improved Signal-to-Noise Ratio
 - Excellent timing capabilities (~ 40 ps) for thin LGADs ($\sim 50 \mu\text{m}$)
 - Low energy X-rays detection (< 5 keV)
- **▼ Performance degradation with radiation damage**
- Challenging performance uniformity with small pixels



LGADs on 4H-SiC silicon carbide: Future of track-timing detectors?

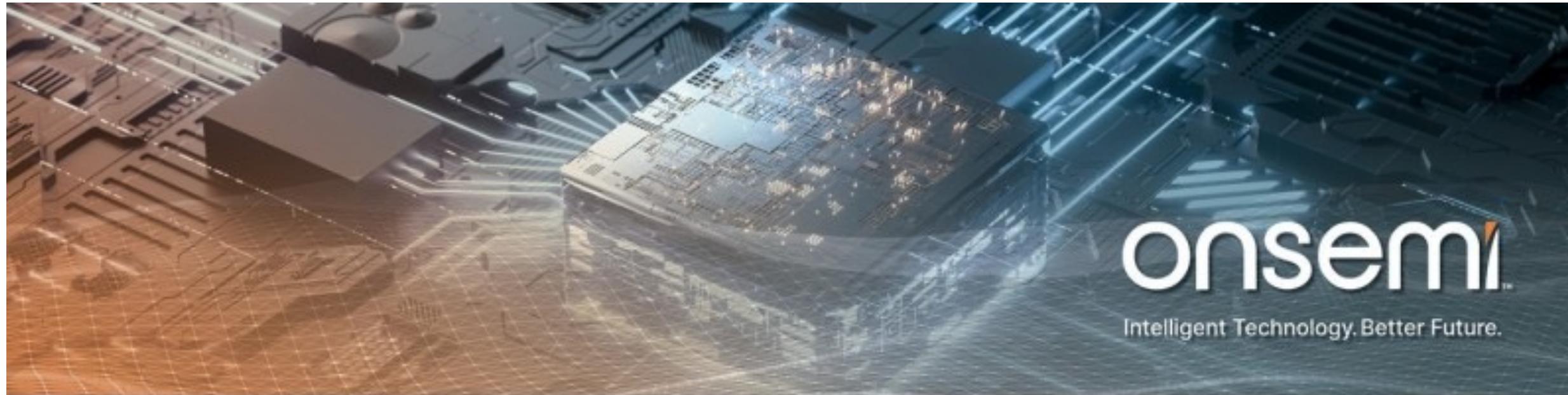
Re-discovery of Silicon-Carbide

- Wider bandgap of $2.4 < E_g < 3.3$ eV compared to Si (1.2eV)
- Advantages
 - Lower dark current
 - Excellent temperature stability (up to 300 °C)
 - High radiation tolerance
 - Material hardness (resistant)
- Disadvantages
 - Lower signal (48 e-h pairs/ μ m)
 - Difficult to manufacture
 - Material hardness (hard to dice, easier to shatter)
- Affordability due to advancements in the automotive industry



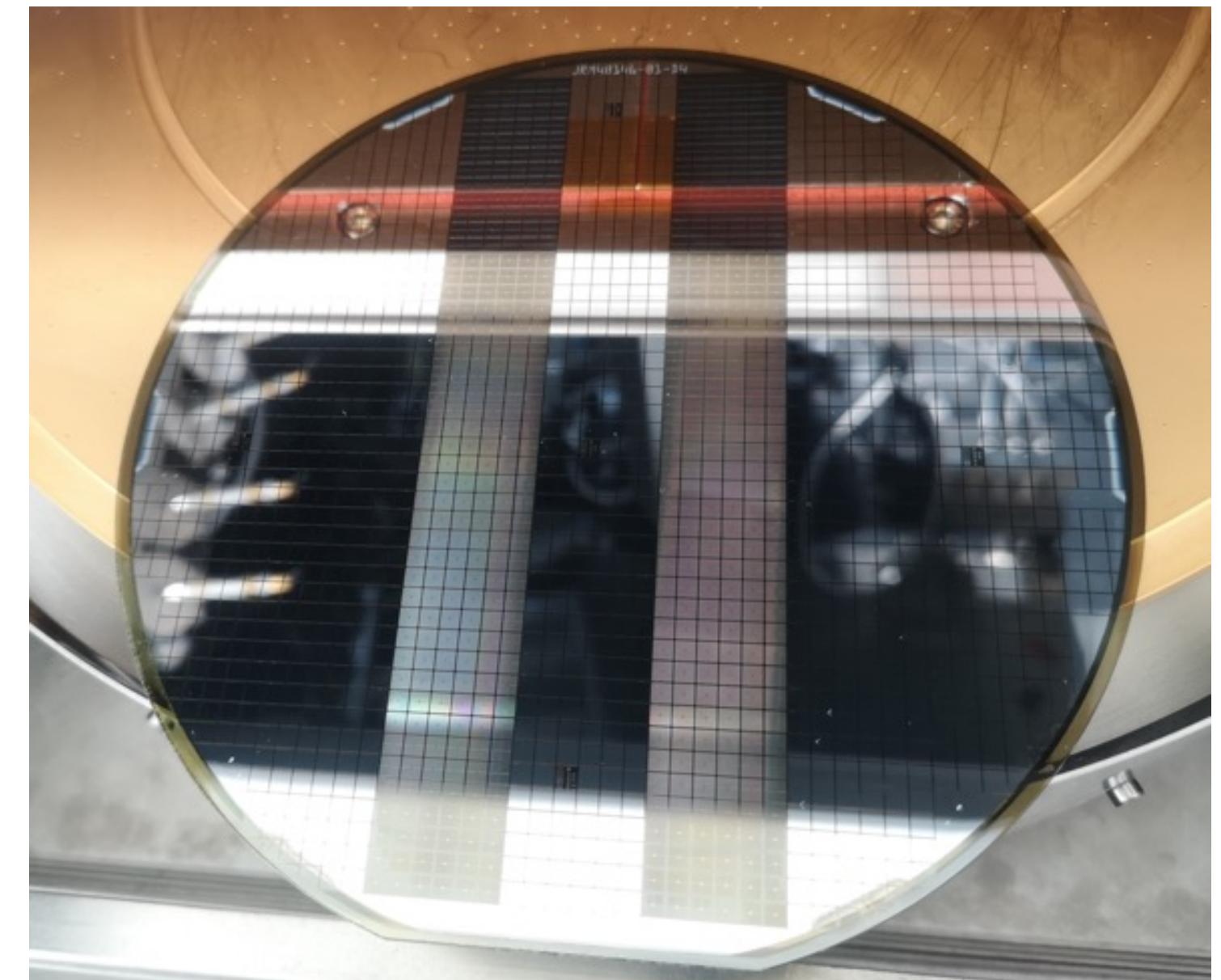
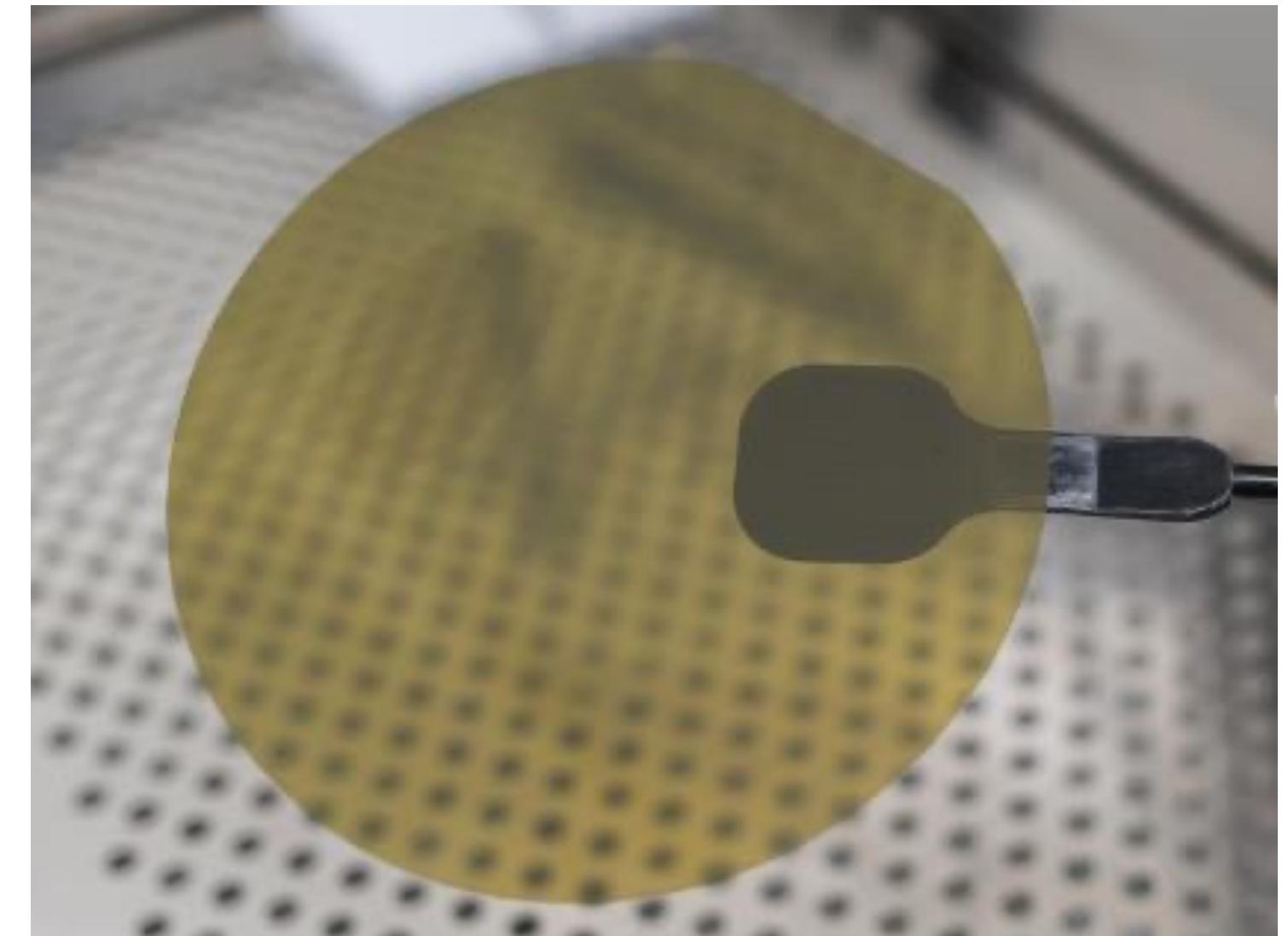
Availability thanks to onsemi

- Silicon sensor manufacturing for ATLAS detector
- New SiC design center in CZ
- Multiple common project developing SiC detectors segmented SiC LGAD



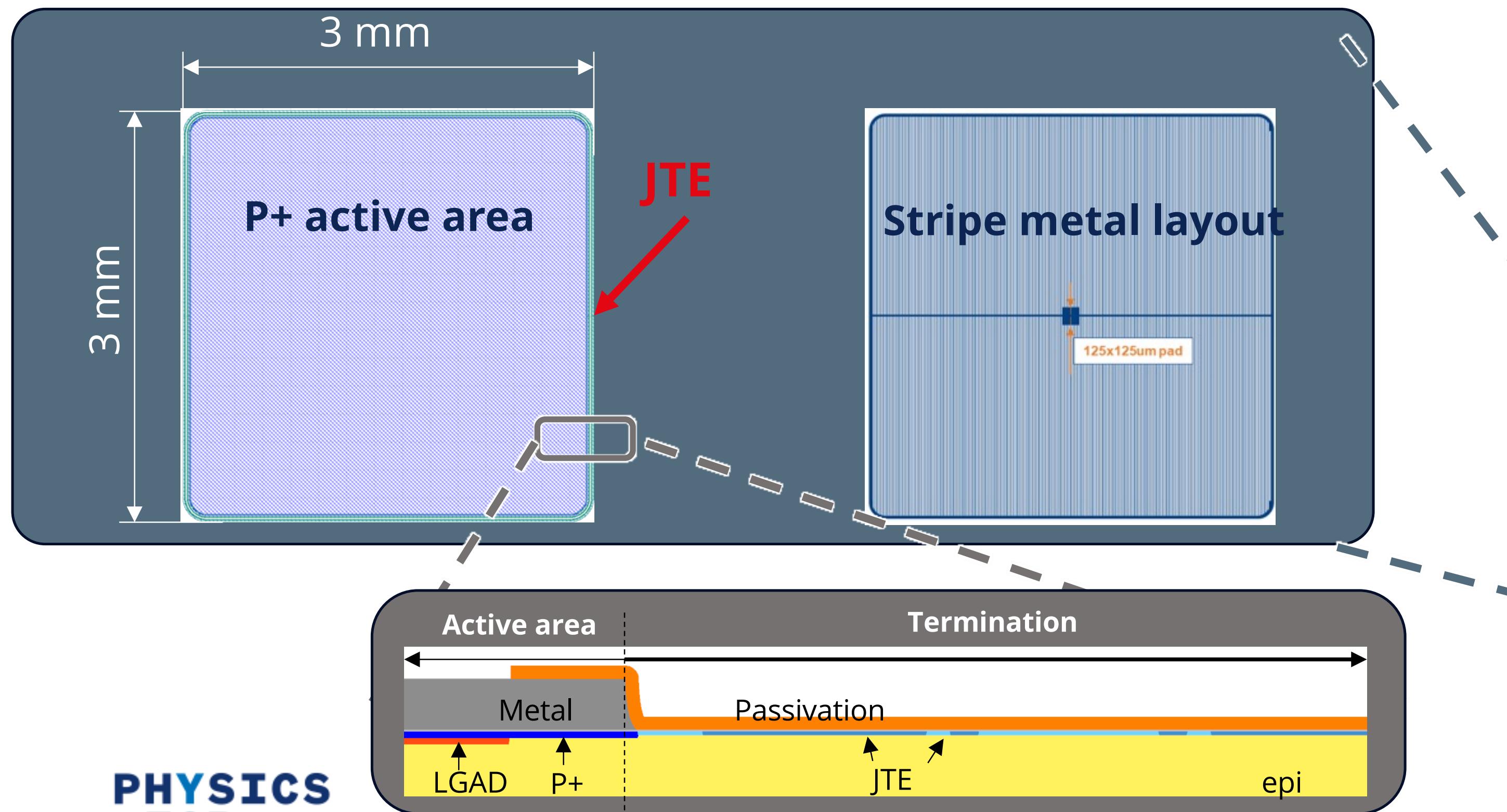
LGADs on SiC – design

- Diode $3 \times 3 \text{ mm}^2$ used for R&D
- Comparison no-gain and LGAD
- $30\text{-}100 \mu\text{m}$ EPI grown on 4H-SiC substrate
- n-type bulk



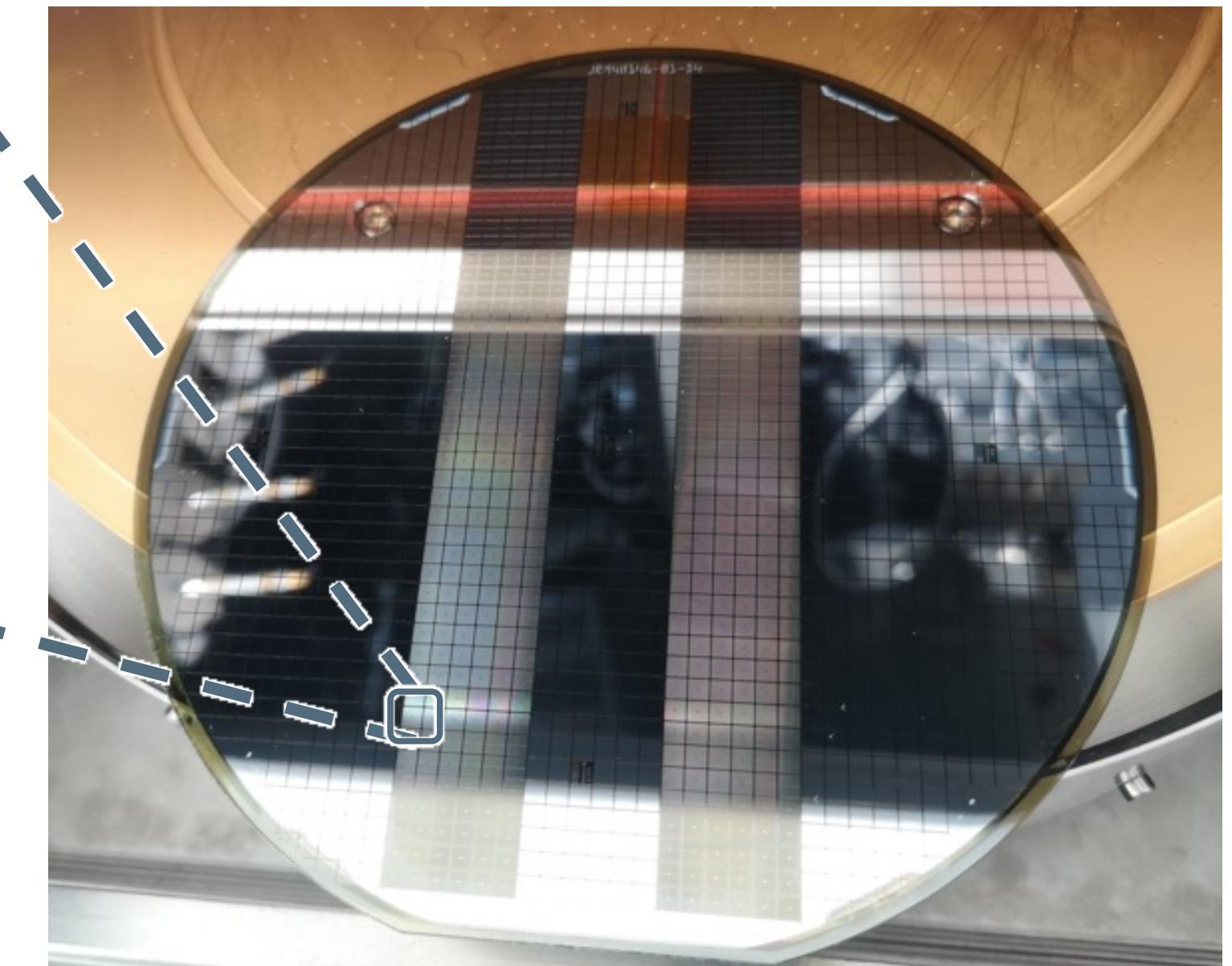
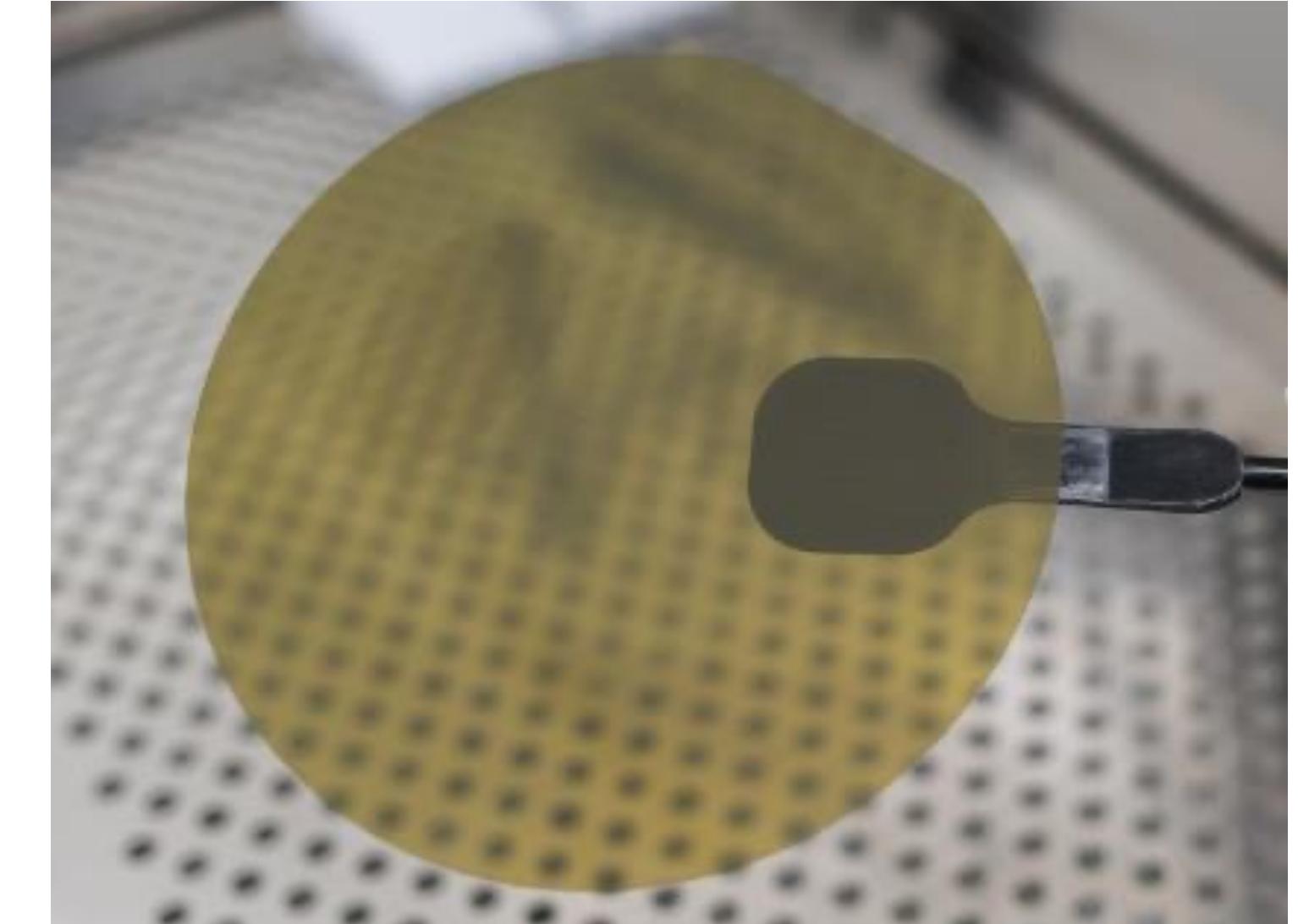
LGADs on SiC – design

- Diode $3 \times 3 \text{ mm}^2$ used for R&D



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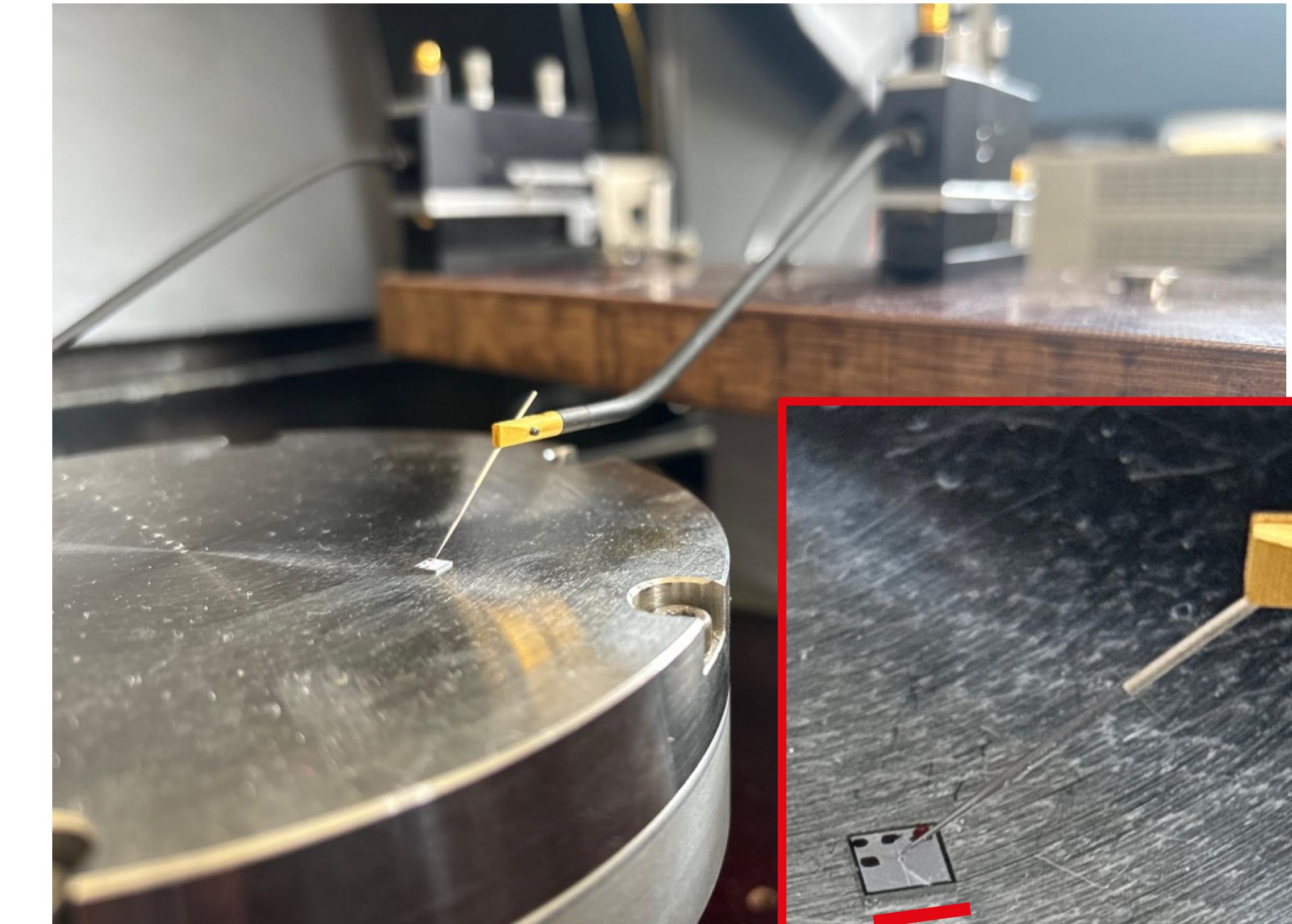
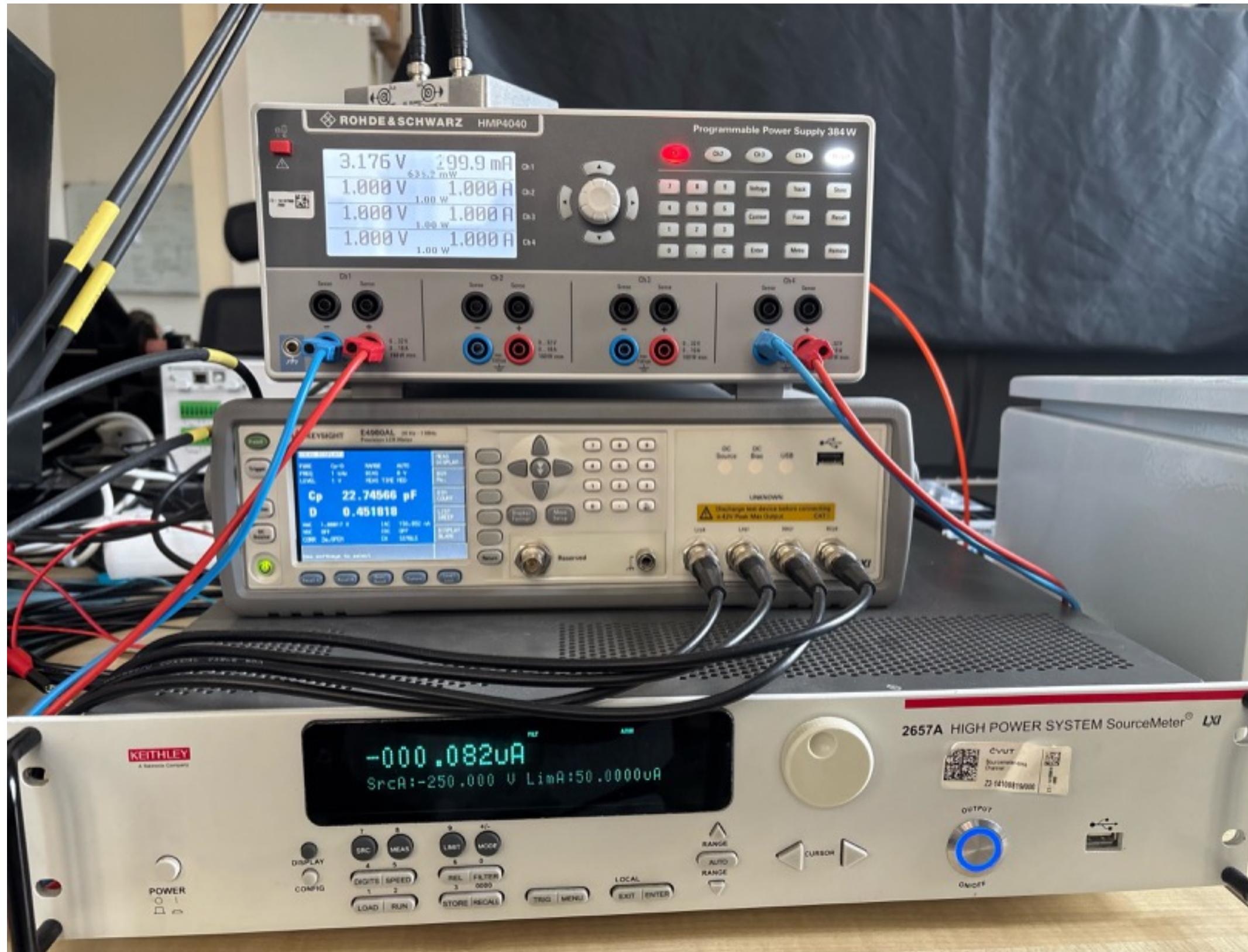
Next Generation Silicon Sensors



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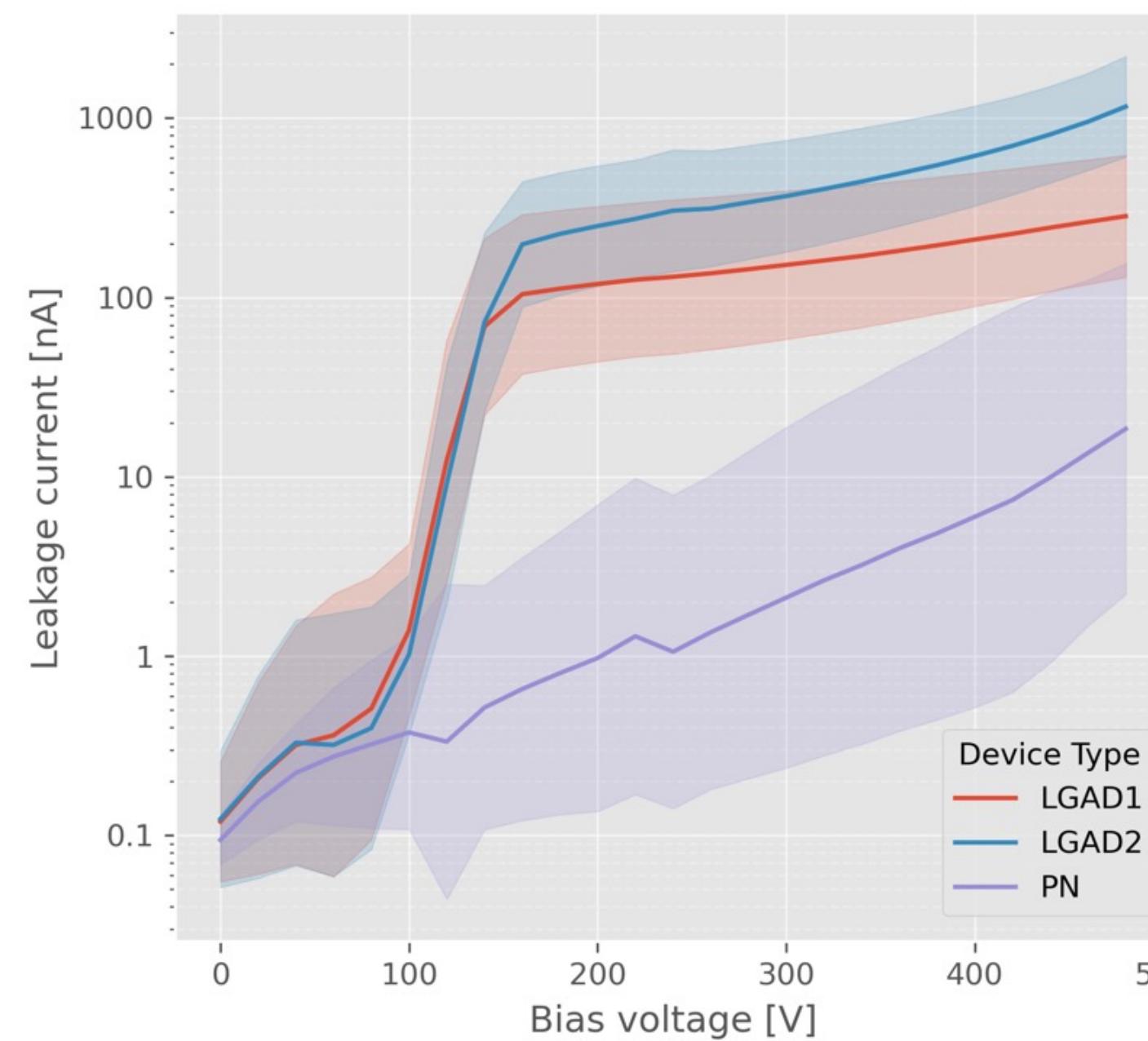
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Electrical characterisation

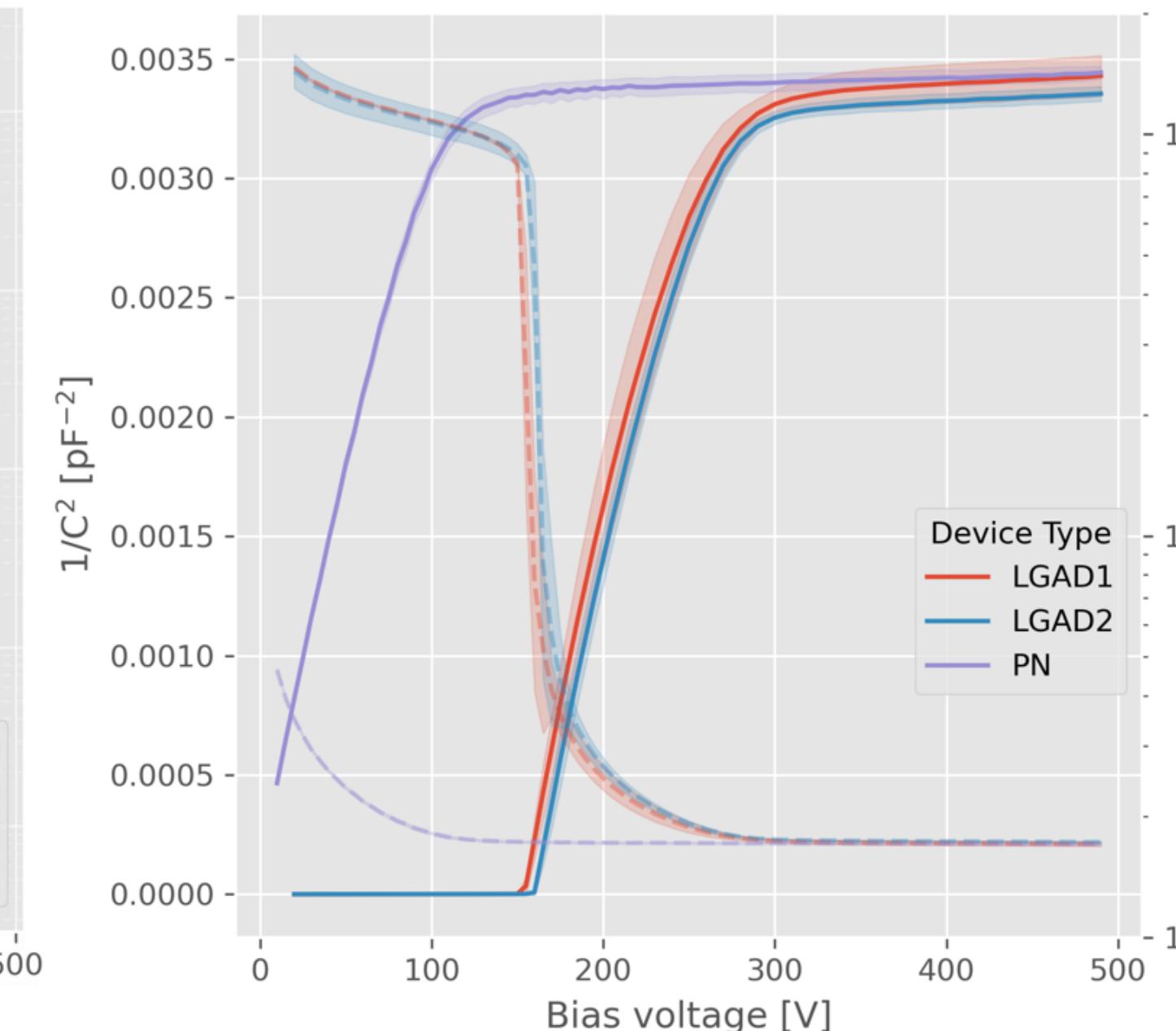


Electrical characterisation - results

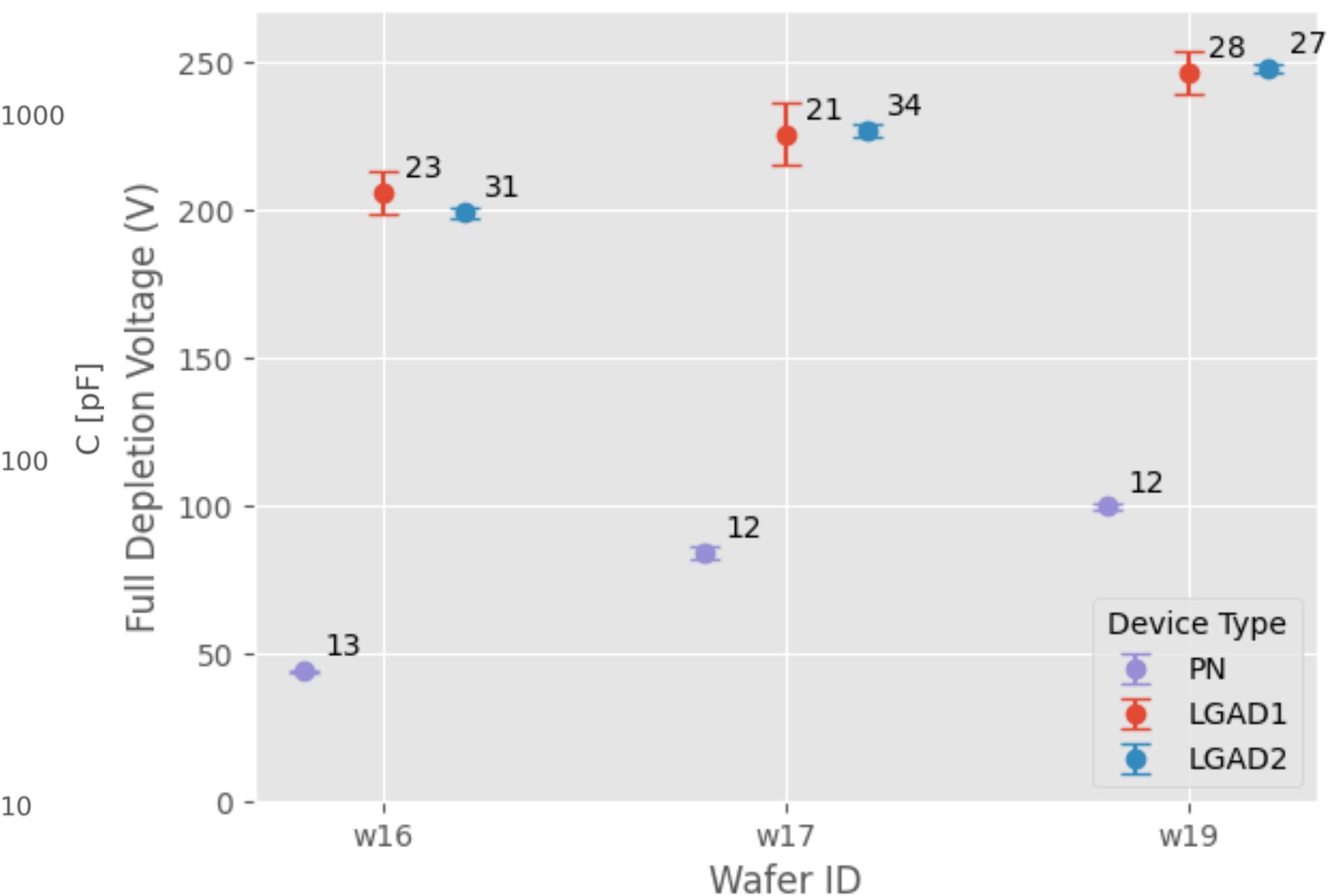
Current-Voltage



Current-Capacitance



Full depletion



Transient Current Technique (TCT)

TPA-TCT setup at CERN SSD

FYLA laser module

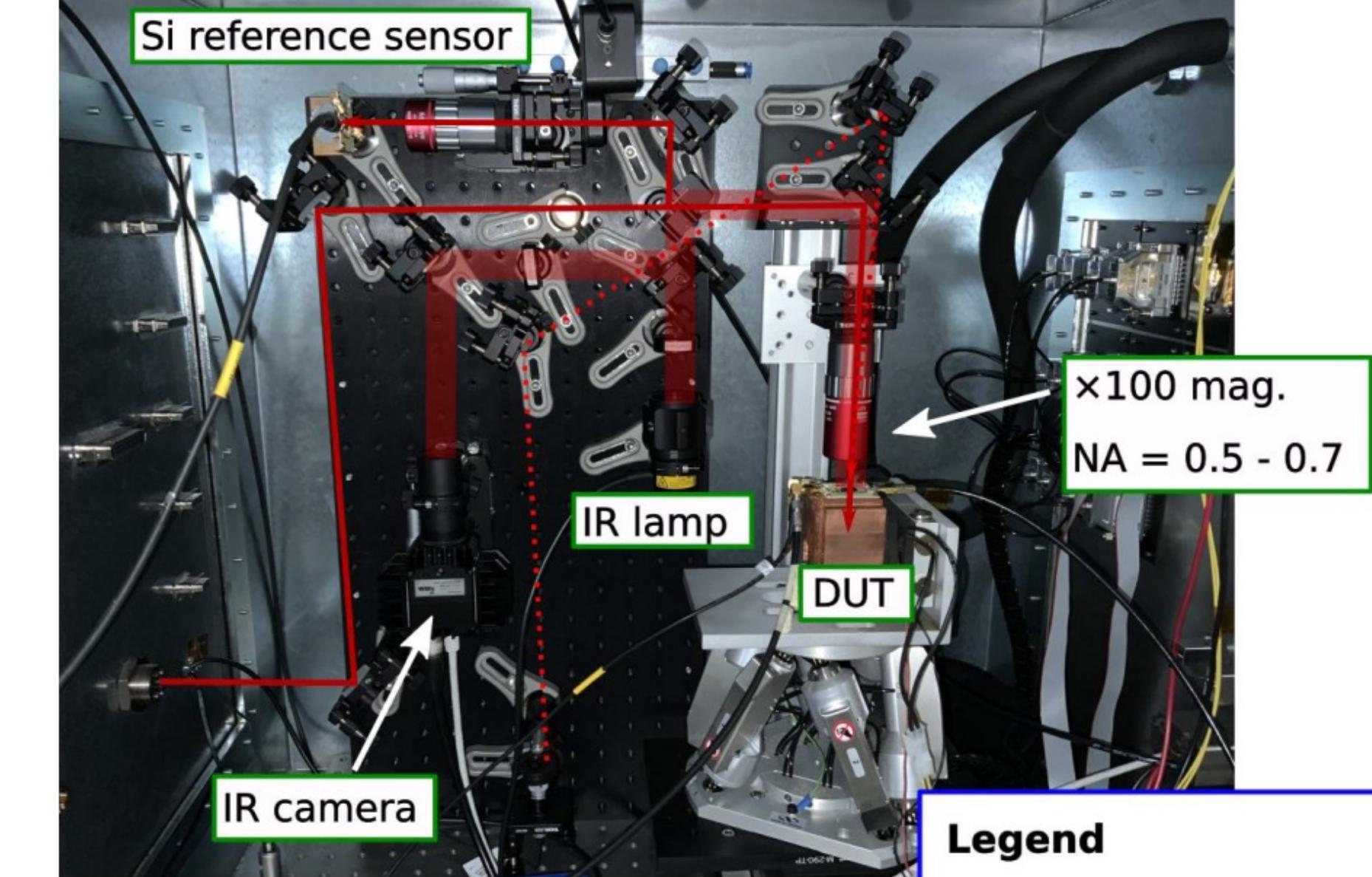
Pulse management
(with SPA reference)

Faraday cage

Inside the Faraday cage

Laser output pulse properties:

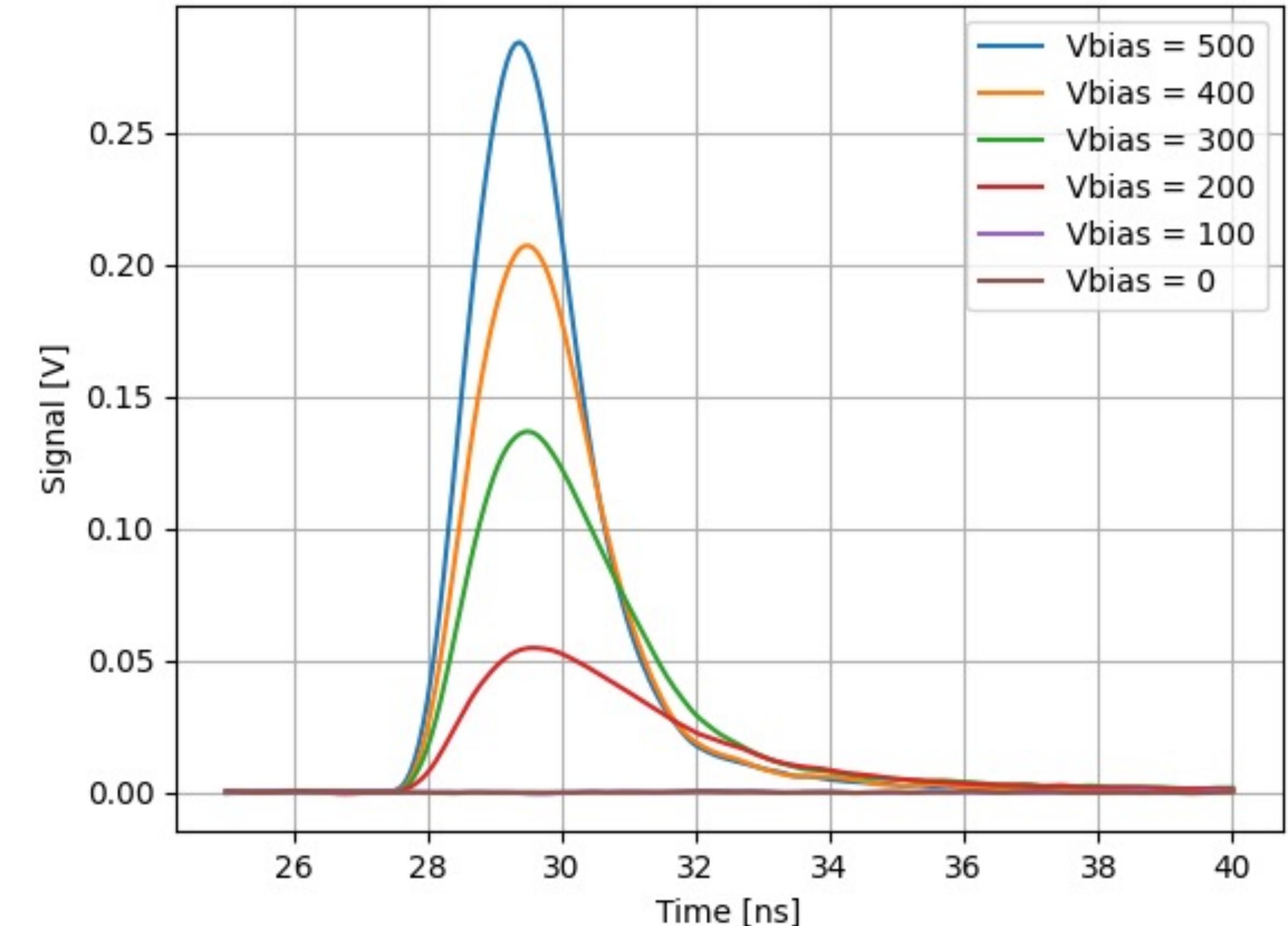
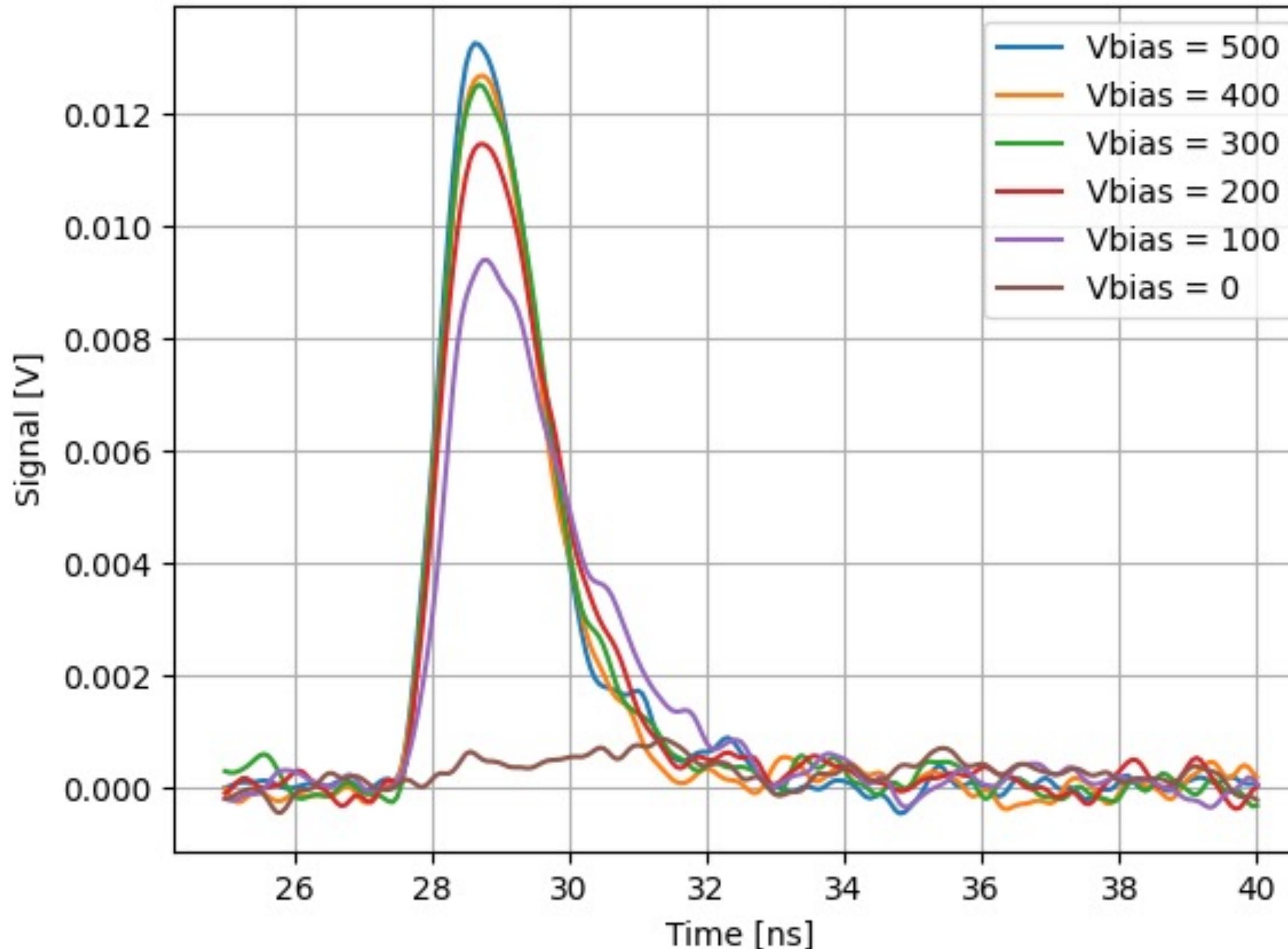
- approx. 430 fs width
- pulse frequency 8.2 MHz to single pulse
- pulse energy up to 10 nJ
- central wavelength 1.55 μm



Legend

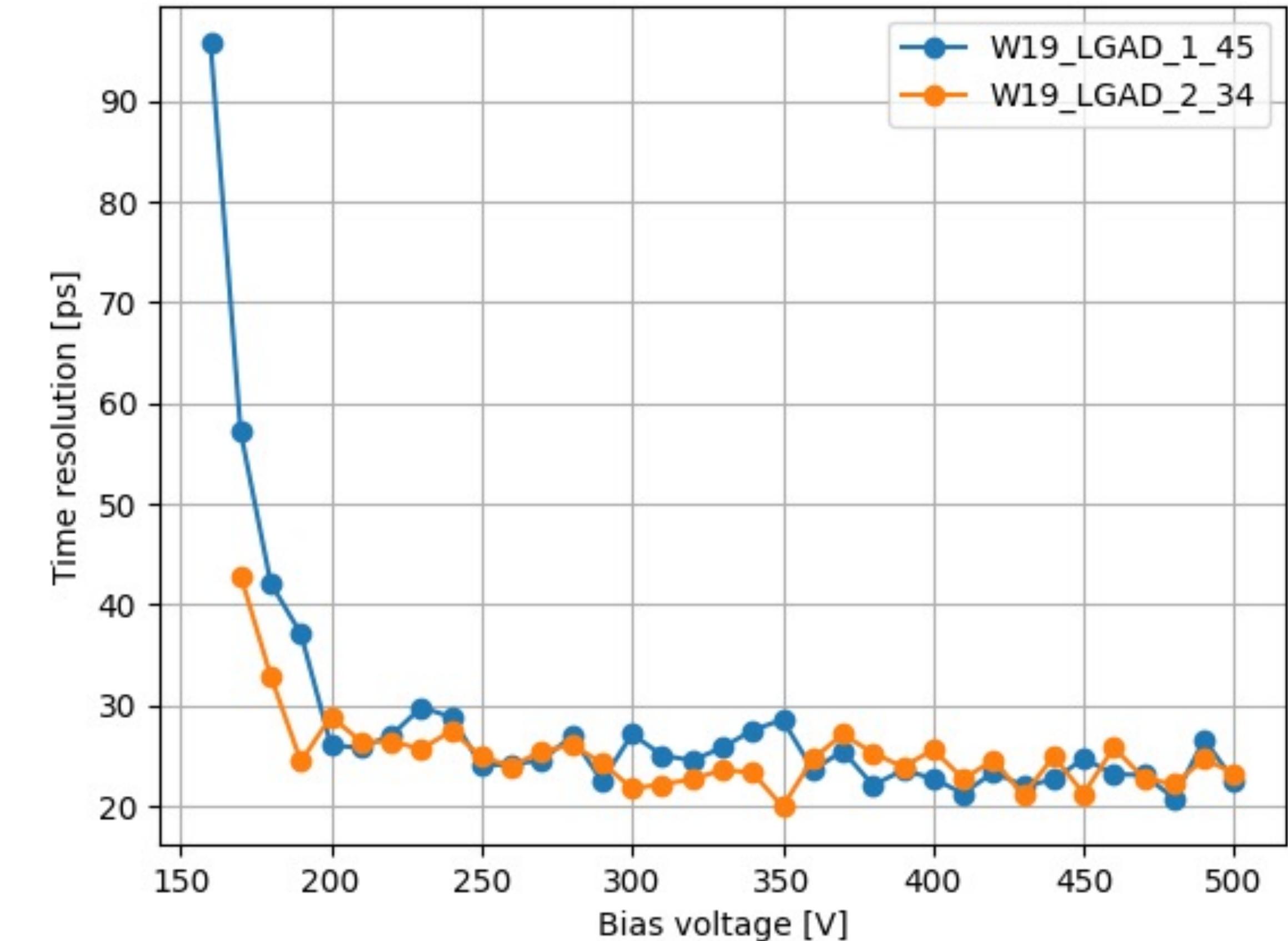
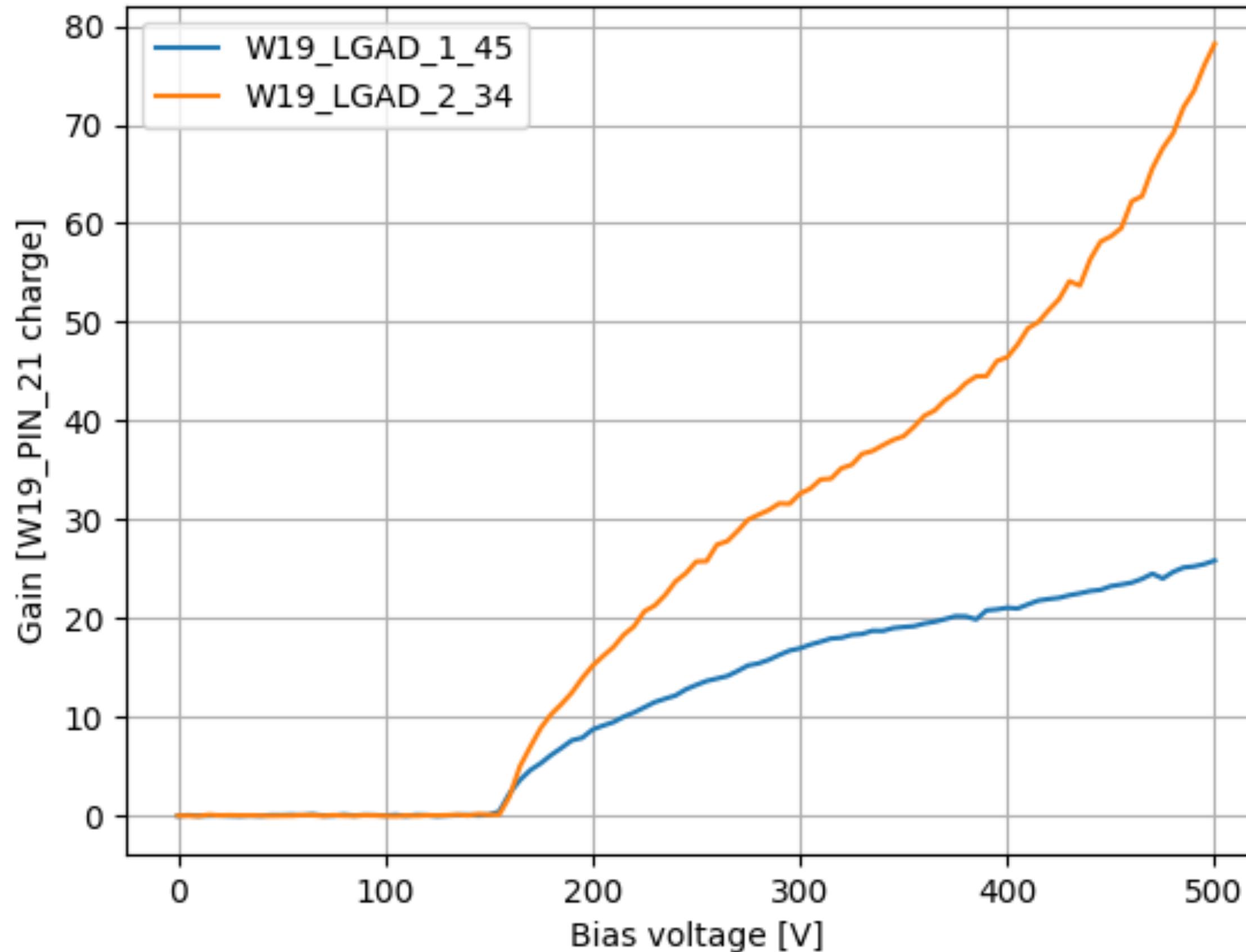
- Laser path
- IR microscope
- Alignment laser

Transient Current Technique (TCT) – results



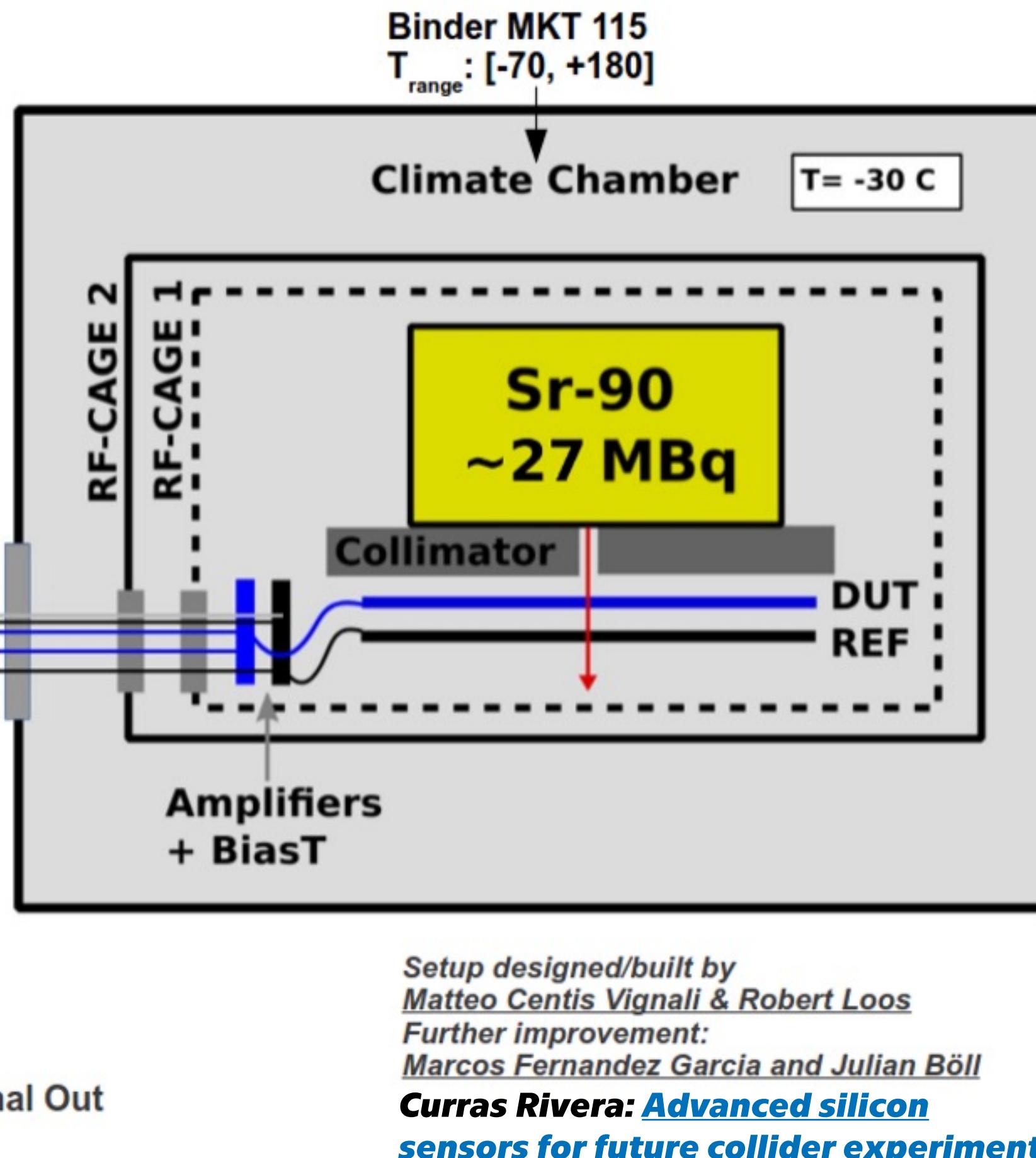
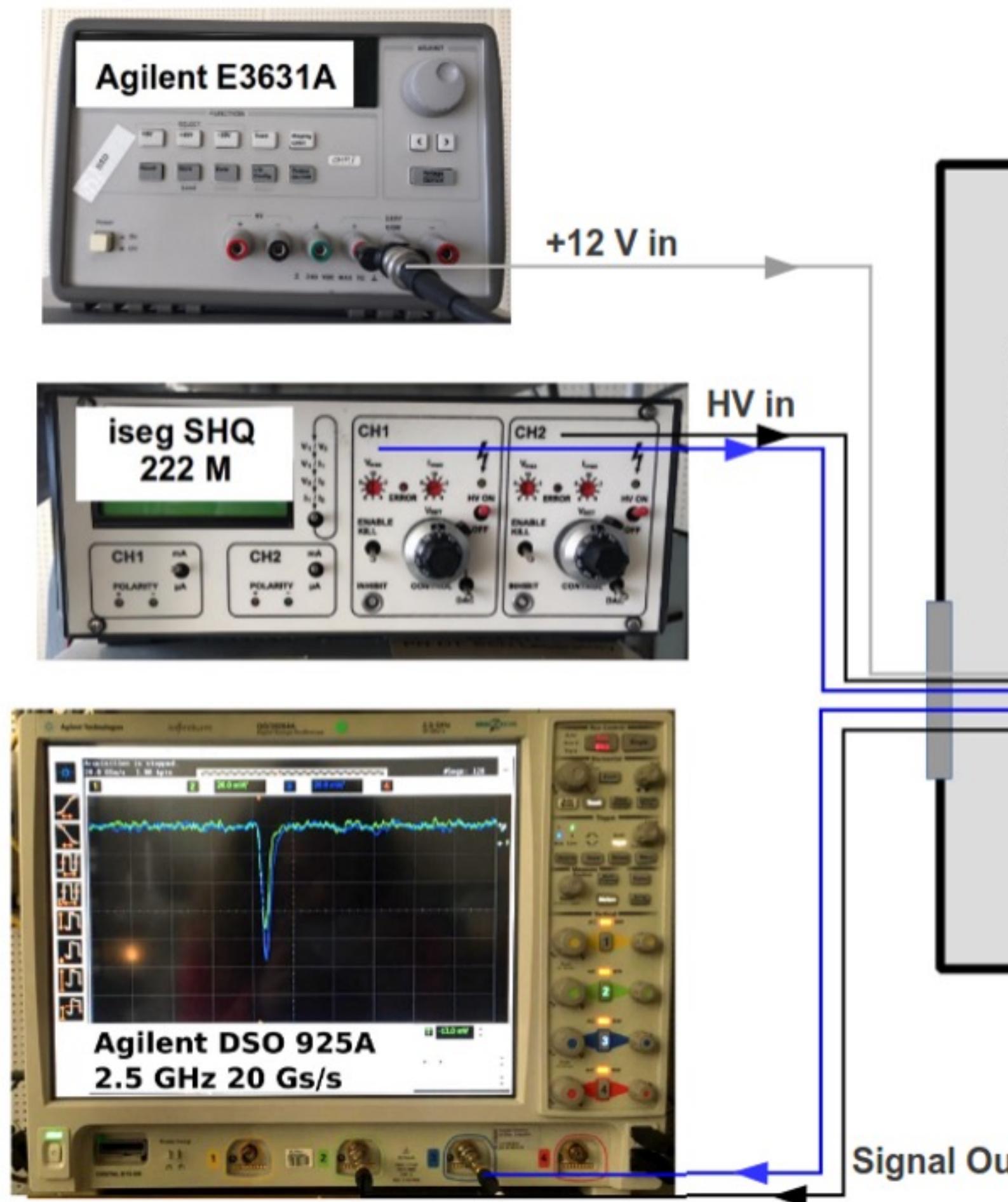
Clear difference of gain on signal response!

Transient Current Technique (TCT) – results



Gain in range of 10-80, non-calibrated signal
response down to 20ps

Beta-source tests

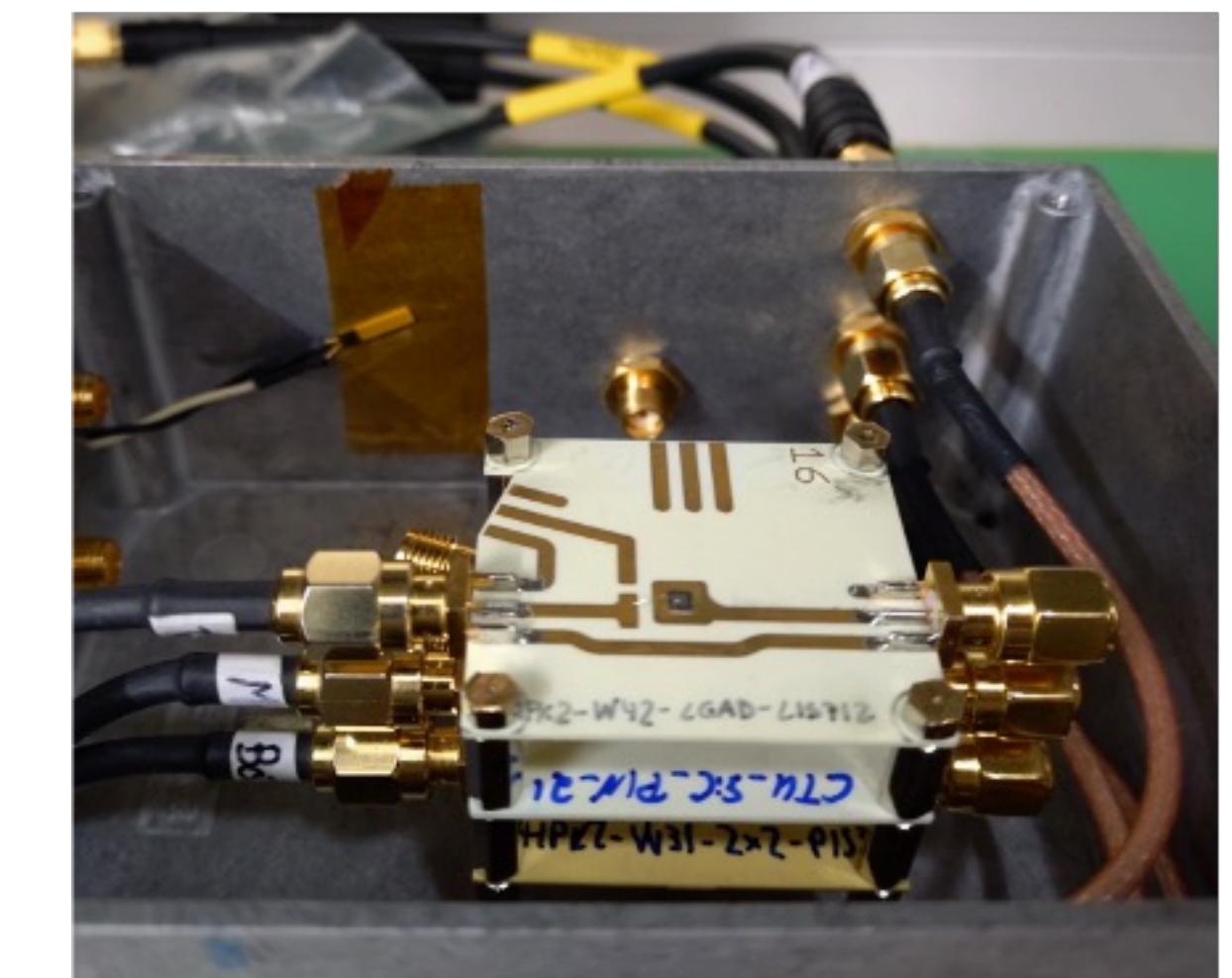


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Next Generation Silicon Sensors

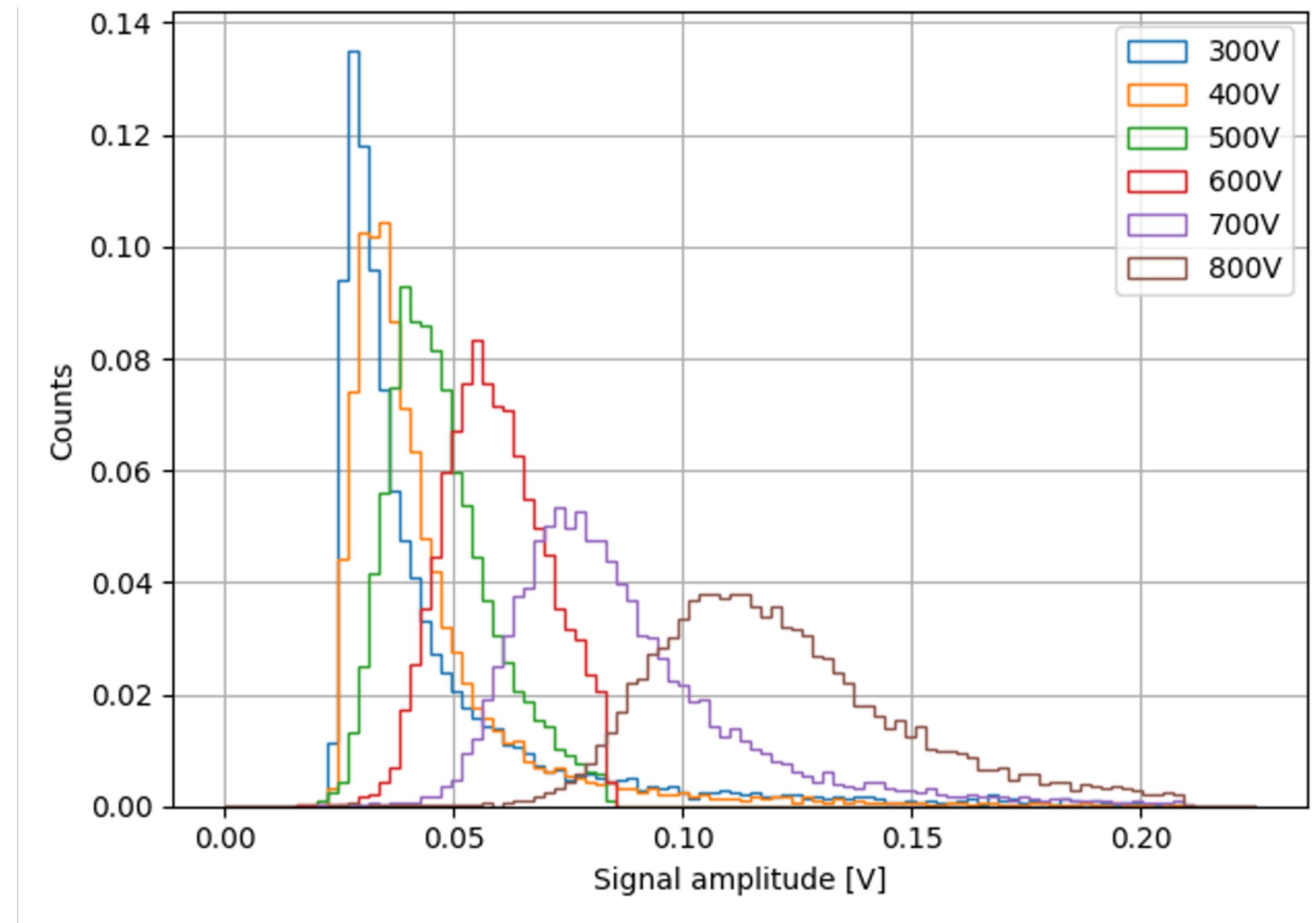
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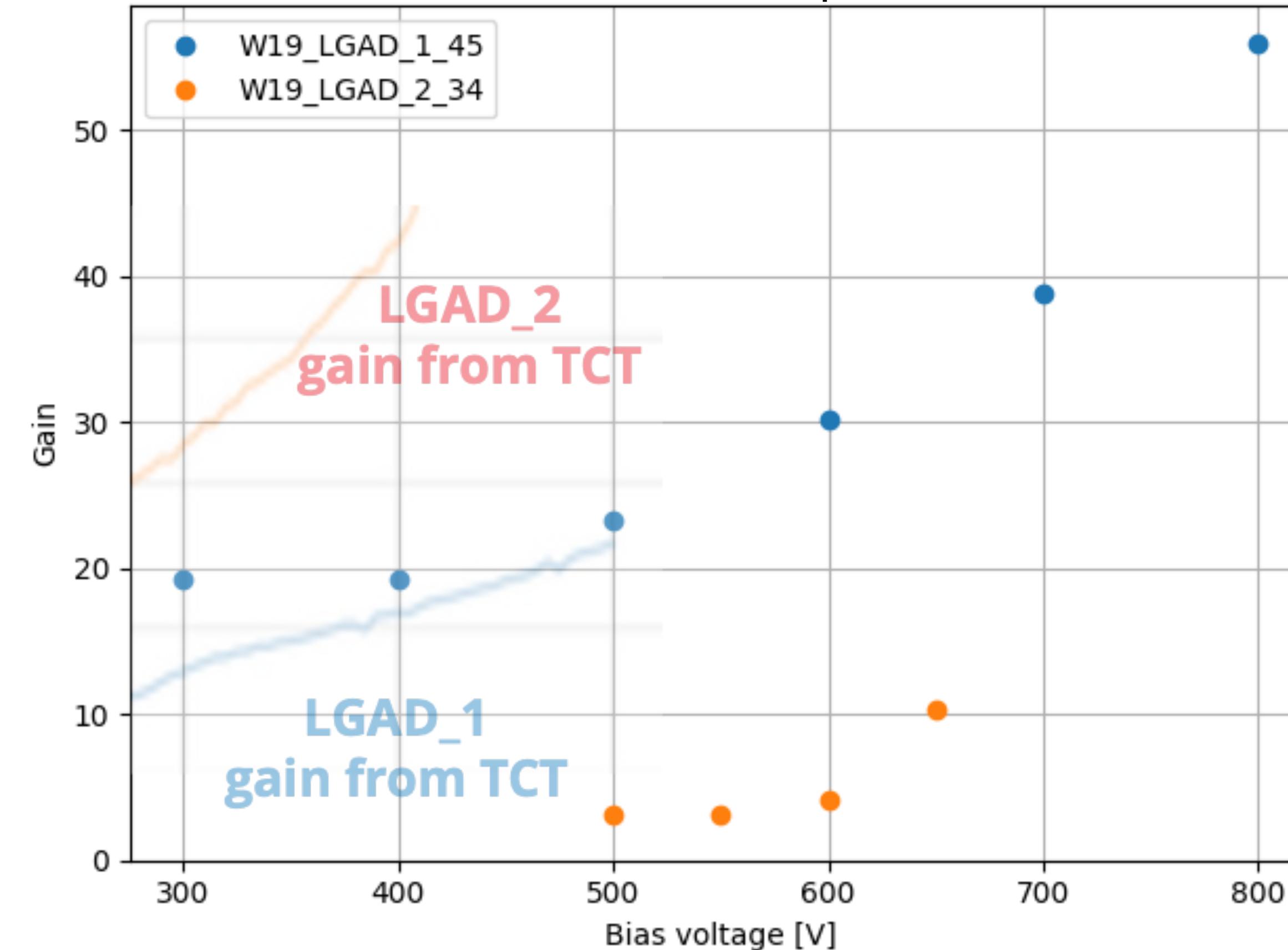
- Each sensor individually read out with current sensitive amplifiers
- Triple coincidence for the oscilloscope trigger

Beta-source tests – results

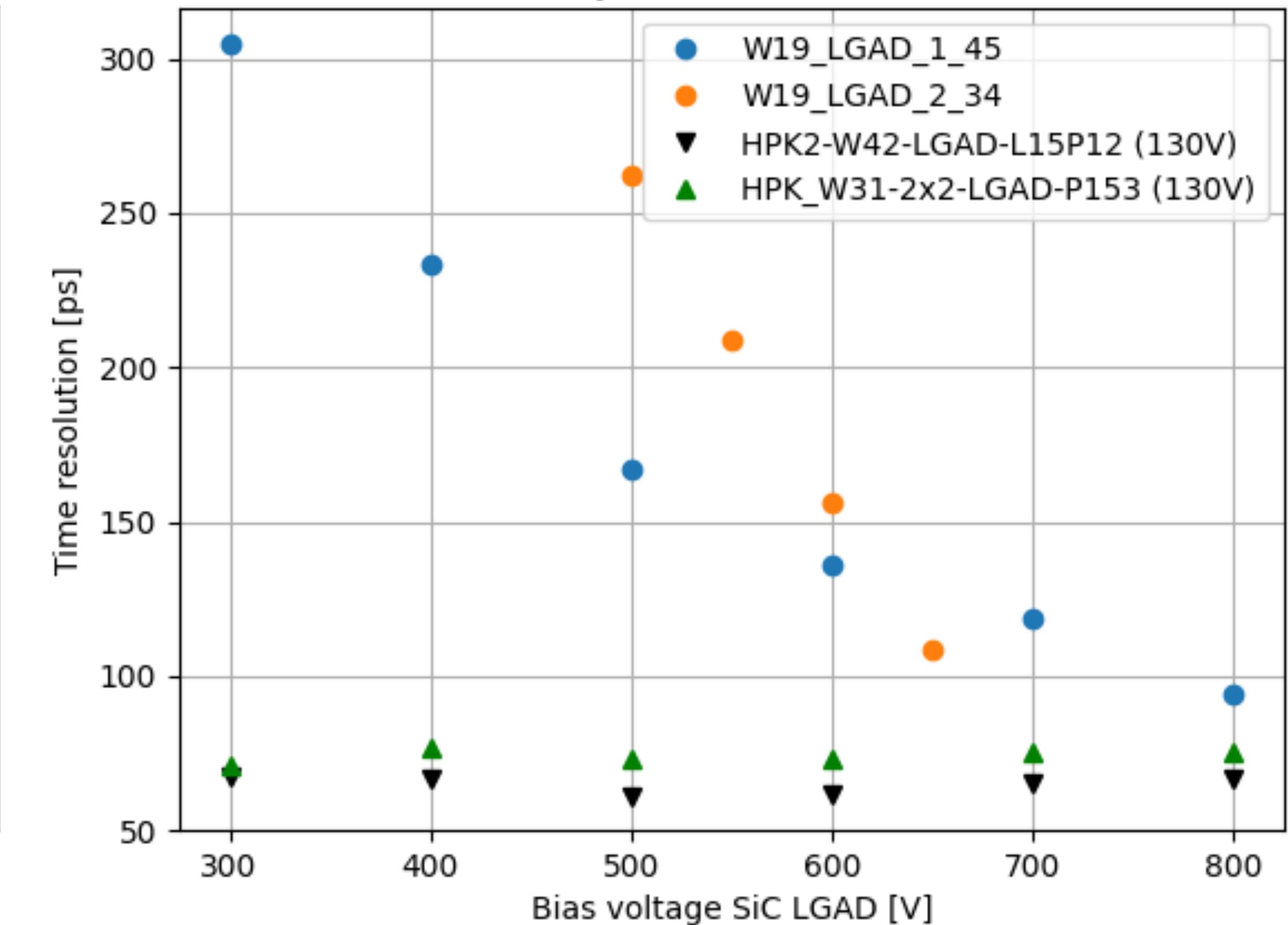


Beta-source tests – results

Gain comparison



Timing-from-coincidence



Future of track-timing detectors..?



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Institute of Physics
of the Czech
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[url: FZU](#)



[url: CAPADS](#)



- **LGADs provide improved timing**
 - Reduces pile-up
 - Not as radiation hard on normal silicon
- **SiC as an alternative**
 - Radiation hard ? - **to be investigated!**
 - On a path to reach the same performance
 - UV detectors ?
 - ... R&D still necessary but promising!

Two papers under review:
<https://arxiv.org/abs/2503.07490>
<https://arxiv.org/abs/2504.09264>

Thank you for your attention



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